ACADEMIC CURRICULA

POST GRADUATE DEGREE PROGRAMMES

Master of Technology

(Choice Based Flexible Credit System)

Regulations 2021

Volume – 24
Syllabi for School of Electrical Engineering
Programmes

Professional Core and Elective Courses



SRM INSTITUTE OF SCIENCE AND TECHNOLOGY

(Deemed to be University u/s 3 of UGC Act, 1956)

Kattankulathur, Chengalpattu District 603203, Tamil Nadu, India

ACADEMIC CURRICULA

VLSI Design

Professional Core Courses

Regulations 2021



SRM INSTITUTE OF SCIENCE AND TECHNOLOGY

(Deemed to be University u/s 3 of UGC Act, 1956)

Kattankulathur, Chengalpattu District 603203, Tamil Nadu, India

Course Code	21ECC530J	Course Name	ELECTRONIC DESIGN AUTOMATION FOR ASIC AND FPGA	Course Category	С	PROFESSIONAL CORE	L 2	T 0	P 2	<u>C</u>

Pre-requisite Courses	N	Co- requisite Courses		Nil	Progressive Courses		Nil
Course Offer	ring Department	Electronics and Communication Engi	neering [Data Book / Codes / Standards		N	lil

Course Learning Rationale (CLR):	The purpose of learning this course is to:
CLR-1:	introduce the basics of hardware description languages and simulation types.
CLR-2:	explain the concepts and CAD tools for simulation and synthesis of digital circuits
CLR-3:	create insights into the theoretical concepts of device modeling and simulation using TCAD tools.
CLR-4:	provide students with the knowledge, skills, and practical experience needed to work effectively with EDA tools and methodologies for analog and digital circuits.
CLR-5:	gives an idea about the tools and techniques for integrated circuit design and Implementation

Course Outcomes	At the end of this course, learners will be able to:	Progra	mme Outco	mes (PO)
(CO):	At the end of this course, learners will be able to.	1	2	3
CO-1:	describe the functionality of a circuit using languages like Verilog or VHDL.	3	2	-
CO-2:	translate high-level descriptions (HDL code) into a gate-level net list that represents the logic of the design with functional design and verification.	3	2	1
CO-3:	explain, the proces <mark>s of creat</mark> ing mathematical representations or models that describe the behaviour of electronic devices.	3	2	1
	simulate and verify the functionality of analog, digital and mixed signal circuits,	3	2	2
CO-5:	implement Frontend and Back-end IC design using EDA tools for analog, Digital, Mixed Signal and RF integrated circuit.	3	2	2

Module-1 – Simulation and Synthesis Using HDL

12 Hour

Simulation-Types of Simulation, Logic Systems, Working of Logic Simulation, Cell Models, Delay Models, State Timing Analysis, Formal Verification, Gate level modelling, Behavioral modelling, Data flow modelling, Switch-Level Simulation, Logic Synthesis, Synthesis in design process of Combinational and sequential circuits, Memory Synthesis, FSM Synthesis, Performance-Driven Synthesis

Practice on different modelling level of simulation and Synthesis of Digital logic circuits: Combinational and Sequential circuits

Module-2 – FPGA Design 12 Hour

FPGA Building blocks, FPGA based digital system design, Usage areas of FPGAs, Configuring and Programming of FPGA, FPGA design and debug cycle, Simulation vs. Debugging in Hardware. Practice on digital system design projects using FPGAs.

Module-3 - Technology TCAD 12 Hour

Device Modelling — From Physics to Electrical Parameter Extraction, MOS Technology and Intrinsic Device Modelling, Intrinsic MOS Transistor and modelling techniques, Substrate Effects on MOS Transistors, Device Technology Alternatives,

Practice on Device Modelling and Simulation using TCAD: Diode, MOS transistor

Module-4 – Analog and Digital Circuit Design and Simulation 12 Hour

Analog and digital design flow, PSPICE Models for Transistors, Design and Analysis of Analog and Digital Circuits, A/D & D/A Sample and Hold Circuits, and Digital System Building Blocks. Practice on Design and Analysis of Analog and Digital Circuits Using PSPICE.

Module-5 – EDA Tools for ASIC Implementation and Verification

ASIC design flow, EDA Tools for Analog and Digital, circuit design and implementation, Design Entry, Design Verification, Physical design and GDS-II file for fabrication. Practice on implementation of analog, digital and RF circuits using EDA tools and obtain GDSII file.

	1. Robert B. Reese, Mitchell A. Thornton, "Introduction to Logic Synthesis using Verilog HDL", 4. Louis Scheffer, Luciano Lavagno, Grant Martin," EDA for IC Implementation, Circuit Design
Learning	Springer, 2022 and Process Technology", Taylor and Francis 2006.
Resources	2. Cem Ünsalan, Bora Tar, Digital System Design with FPGA, Implementation using Verilog and 5. M.J.S.Smith, "Application-Specific Integrated Circuits", Addison Wesley. 1997
Resources	VHDL", Mc Graw Hill, 2017. 6. M.H.Rashid, "SPICE FOR Circuits and Electronics Using PSPICE", (2/E) Prentice Hall, 1992.
	3. J.Bhaskar, "A Verilog HDL Synthesis", BSP, 2003.

Learning Assessme	ent	7 .0"	ATT I	13 m			
	Bloom's Level of Thinking	CLA-1 Avera		Life-Long CL	g Learning A-2	Final Ex	mative amination eightage)
	Ĭ.	Theory (43	5%) Practice	Theory (1)	5%) Practice	Theory	Practice
Level 1	Remember	20 %	A 52 May 10	M .	20 %	30 %	-
Level 2	Understand	20 %	28 E 18 E 18		20 %	40 %	-
Level 3	Apply	30%	1 Jan 1997	A company	30%	30 %	-
Level 4	Analyze	30%		1	30%	-	-
Level 5	Evaluate			3444			-
Level 6	Create	-	Carlor of Parkers and	- 19			-
	Tot <mark>al</mark>	100) %	. 10	0 %	10) %

Course Designers	
Experts from Industry	Experts from Higher Technical Institutions Internal Experts
Mr. Sethupathy Balakrishnan, Lead Application Engineer, Cadence Designs Systems	1. Prof Meenakshi M, Dept of Electronics and Communication Engineering, College of Engineering Guindy, Anna University 1. Dr. J. Manjula, SRMIST
	2. Prof. Binsu J Kailath, Dept of Electronics Engineering, IIITDM, Kancheepuram

Course	21ECC531J	Course	DIGITAL SYSTEMS DESIGN USING HDL	Course	С	PROFESSIONAL CORE	L	Τ	Р	С
Code		Name		Category			3	0	2	4

Pre-requisite	/	Vil	Co- requisite		Nil	Progressive		Nil	
Courses			Courses			Courses			
Course Offering	Department	Electronics ar	nd Communication Eng	ineering	Data Book / Codes /			Nil	
	-		/ 6		Standards	17.3			
							7		

Course Learning	The purpose of learning this course is to:
Rationale (CLR):	
CLR-1:	understand behavioural and RTL modelling of digital circuits
CLR-2:	understand the basic CMOS circuit, characteristics, and performance
CLR-3:	learn the designing of combinational circuits using different CMOS logic
CLR-4:	learn the designing of sequential circuits and FSM
CLR-5:	get an idea about des <mark>igning D</mark> atapath and memory systems and how to implement such design

Course	At the end of this course, learners will be able to:	Progra	mme Outcome	es (PO)
Outcomes (CO):		1	2	3
CO-1:	apply Verilog HDL to model digital systems, utilizing various abstraction levels	3	2	
CO-2:	analyse the basic CMOS circuit, including characteristics and performance metrics, demonstrating comprehension.	3	2	
CO-3:	evaluate and synthesize the design of combinational circuits using different CMOS logic, showcasing application of knowledge.	3	2	
CO-4:	synthesize the circuit design of latches, flip-flops, and Finite State Machines (FSMs) based on comprehension and application.		2	3
CO-5:	apply various optimization methods in the design of data paths and memory systems, demonstrating synthesis at higher cognitive levels.		2	3

Module-1 - Basic Concepts - Verilog

15 Hour

Basic concepts, Identifiers, Value set, Data types, Parameters, Operands, Operators, Modules and ports, Gate-level Modelling, Behavioural Modelling, Tri state gates, MOS Switches, Bidirectional switches, Switch level modelling, Combinational UDP, System task, System functions, Introduction to synthesis, Verilog HDL synthesis, Synthesis Design flow, System Verilog Practice on: Design and simulate the combinational circuits, Design and Implementation using task and function, Design and Verify Circuit Using Switch Level Modelling.

Module-2 - Principle of MOS Transistor's and CMOS Inverter

15 Hour

MOS Transistors, Threshold Voltage, Characteristics of MOS Transistor, Derivation of Drain Current, Short Channel Effects, Transfer Characteristics of CMOS Inverter, Transfer Characteristics of CMOS Inverter, Design of Logic Gates Circuit Using NMOS load, Design of Logic Gates Using PMOS load, Design of Logic Gates Using CMOS, Design and Verify Sequential Circuits, Stick Diagrams, Stick Diagrams Example, Case Study: Optimization of a CMOS inverter for minimum power consumption and delay.

Practice on: Implement CMOS Inverter using NMOS. PMOS, and CMOS configurations, Implementation of logic gates using CMOS, Implementation of Boolean expression using CMOS

Module-3 - CMOS - Combinational Circuits

15 Hour

Static CMOS design, complementary CMOS, static properties, complementary CMOS design, power consumption in CMOS logic gates, dynamic or glitching transitions. Design techniques to reduce switching activity, ratioed logic-DC VSL - pass transistor logic, differential pass transistor logic, design using differential pass transistor logic, sizing of level restorer, Sizing in pass transistor-Dynamic CMOS design - Basic principles - Domino logic optimization of Domino logic. NPCMOS-logic style selection. Designing logic for reduced supply voltages, design and analyse low power circuit, Case Study: Design and analysis of a low-power CMOS combinational circuit for a specific application, considering different logic optimization techniques.

Practice on: Design and implement Booth Multiplier, Design and simulate FSM design, Implement and optimize a CMOS circuit using Domino logic

Module-4 - CMOS - Sequential Circuits

15 Hour

Timing Metrics for Sequential Circuit, Latches Vs Registers - Static Latches and Registers Biostability Principle, Multiplexer Based Latches, Master Slave Edge Triggered Registers, Non-ideal Clock Signals, Low Voltage Static Latches - Static SR Flip Flop, C2MOS Register, Dual Edge Registers, True Single Phase Clocked Registers, Pipelining to Optimize Sequential Circuit - Pipelining to Optimize

Sequential Circuit, Choosing a Clocking Strategy - Problem Solving, Design Circuit Using Pipeline Concept, Case Studies: Implementation of a Pipelined Processor with emphasis on optimizing clock cycles. Design and analysis of a low-power sequential circuit using advanced clocking strategies.

Practice on: Design and Verify Pipelined Based Circuit Latch, Design and verify the static latches, Design and Implement FIR Filter/FIR Filter With Pipelining

Module-5 – Datapath and Memory System Design

15 Hour

Adder – Carry Select Adder, Adder – Carry Save Adder, Multiplier – Baugh-Wooley, Multiplier – Wallace Tree, Booth Multiplier, Universal Shift Register, Barrel Shifter, Power and Speed Trade-off's in Datapath Structures, Memory – RAM Static RAM, Dynamic RAM, Serial Access Memory – ROM, Content Addressable Memory, Content Addressable Memory, Finite-State Machines, Types of Finite-State Machines, Case Studies: The Programmable Logic Array (PLA), A 4-bit SRAM.

Practice on: Design and Simulate Universal Shift Register, Design and Simulate Memory Circuits, Design a Traffic Light Controller for an Intersection with a Main Street, a Side Street, and a Pedestrian Crossing or a Vending Machine

Learning Resources

- 1. Samir palnitkar, "Verilog HDL", Pearson education, Second Edition, 2003.
- 2. Jan.M.Rabaey., Anitha Chandrakasan Borivoje Nikolic, "Digital Integrated Circuits", Second Edition
- Michael D. Ciletti, Advanced Digital Design with Verilog HDL, Second Edition, Pearson, 2011.
- 4. Neil H.E Weste and Kamran Eshraghian, "Principles of CMOS VLSI Design", 2nd Edition, Addition Wesley, 1998.
- 5. Sung Mu Kang, Yusuf Leblebici "CMOS Digital Integrated Circuits", 3rd edition, Tata McGraw-Hill, 2002.

earning Assessme	ent		医动脉 计扩张系统	- Carl Busha			
<u>-</u>			Summative				
	Bloom's Level of T <mark>hinking</mark>	CLA-1 Avera	native ge of unit test 5%)	Cl	g Leaming _A-2 5%)	Final Exa	native amination eightage)
	-	Theory	Practice	Theory	Practice	T <mark>heory</mark>	Practice
Level 1	Remember	20 %	10 m 10 m 2 m 10 m 10 m 10 m 10 m 10 m 1		20 %	20 %	-
Level 2	Understand	20 %	and the same of th	A. B. 15	20 %	20 %	-
Level 3	Apply	30 %		1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	30 %	30 %	-
Level 4	Analyze	30 %		/	30 %	30 %	-
Level 5	Evaluate			77.5		2	-
Level 6	Create	PCA - Y	-				-
	Total	10	0 %	10	0 %	10	0 %

Course Designers		
Experts from Industry	Experts from Higher Technical Institutions	Internal Experts
Mr. Sethupathy Balakrishnan, Lead Application Engineer, Cadence Designs Systems	Prof Meenakshi M, Dept of Electronics and Communication Engineering, College of Engineering Guindy, Anna University	1. Dr. <mark>R. Prithiv</mark> iraj SRMIST
	2. Prof. Binsu J Kailath, Dept of Electronics Engineering, IIITDM, Kancheepuram	2. Dr. A. Maria Jossy, SRMIST
		3. Dr. E. Chitra, SRMIST

Course	21ECC532T Cours	SOLID STATE DEVICES AND MODELING	Course C	PROFESSIONAL CORE	L T	Р	С
Code	Name		Category		3 1	0	4

Pre-requisite	Nil	Co- requisite	Nil	Progressiv		Nil
Courses		Courses		Courses	" II	
Course Offering	Department Ele	ectronics and Communication E <mark>ngin</mark>	neering Data Book / C	odes / Standards		Nil

Course Learning	The purpose of learning this course is to:
Rationale (CLR):	
CLR-1:	identify the basic concept and application of quantum mechanics
CLR-2:	illustrate the basics of semiconductor in equilibrium and non-equilibrium
CLR-3:	analyze the physical effects in PN junction and metal-semiconductor junction
CLR-4:	explain the physics of MO <mark>S capacit</mark> or and working of MOSFETs
CLR-5:	illustrate the scaling and short channel effects in MOSFET compact modelling

Course	At the end of this course, learners will be able to:	Programme Outcomes (PO)			
Outcomes (CO):		1	2	3	
CO-1:	understand the principle of Schrodinger's wave equation and analyze the concept of energy band diagram	3	2	-	
CO-2:	apply quantum theo <mark>ry to se</mark> miconductor in equilibrium and non-equilibrium	3	2	-	
CO-3:	apply physical effe <mark>cts in PN</mark> Junctions and metal-semiconductor junction	3	2	-	
CO-4:	identify the basic concepts used in MOS capacitor and MOSFET	3	-	3	
CO-5:	apply the concepts of scaling and short channel effects in MOSFET Modelling	3	2	-	

Module-1 - Introduction to Quantum Mechanics

12 Hour

Principles of Quantum Mechanics: Energy Quanta, Schrodinger's Wave Equation, Physical Meaning of the Wave Function, Applications of Schrodinger's Wave Equation: Electron in Free Space, The Infinite Potential Well, The Finite Potential Well, Allowed and Forbidden Energy Bands, The E-k-Space Diagram, The Energy Band and the Band Model, Drift Current, Electron Effective Mass, Concept of the Hole, Metals, Insulators, and Semiconductors, Direct and Indirect Band Gap Semiconductors.

Module-2 - Semiconductor in Equilibrium and Non-equilibrium

12 Hou

Density of States Function, The Fermi–Dirac Probability Function, Charge Carriers in Semiconductors, Thermal Equilibrium Distribution of Electrons and Holes, The Intrinsic Carrier Concentration & The Intrinsic Fermi-Level Position, The Extrinsic Semiconductor: Equilibrium Distribution of Electrons and Holes, The nopo, Product, Fermi-Dirac integral, Position of Fermi Energy Level, Degenerate and Nondegenerate Semiconductors, Charge Neutrality: Compensated Semiconductors, Complete Ionization and Freeze-Out, Drift and Diffusion Process, Carrier Generation and Recombination, Characteristics of Excess Carriers.

Module-3 - The P-N and Metal Semiconductor Junction

12 Hour

Basic Structure of the PN Junction, Built-in Potential Barrier at zero bias, Electric Field at zero bias, Space charge width at zero bias, Reverse App<mark>lied Bias, Space Charge Width and Electric Field at reverse bias, Nonuniformly Doped Junctions: One-Sided Junctions, Linearly Graded Junction, PN Junction Current, Tunnelling Mechanism, Junction Breakdown: Zener Effect and The Avalanche Effect, The Schottky Barrier Diode. Metal-Semiconductor Ohmic Contact.</mark>

Module-4 - Metal Insulator Semiconductor Devices

12 Hour

The Two-Terminal MOS Structure: Energy-Band Diagrams in Accumulation, Depletion and Inversion Regions, Depletion Layer Thickness, Threshold Voltage, Flat-Band Voltage, Capacitance-Voltage Characteristics for N-MOS and P-MOS, Ideal C-V Characteristics, Frequency Effects, The Basic MOSFET Operation: Depletion and Enhancement MOSFETs, Substrate Bias Effects, Subthreshold Conduction. Subthreshold slope

Module-5 - MOS Compact Modelling

MOSFET Scaling, Moore Law, Short channel effects: Channel length modulation, Velocity saturation, Mobility degradation, Hot carrier effects, Punch through, Ballistic Transport, Square law Model; Level 1 in SPICE, Level 3 in SPICE, History of BSIM models, BSIM family of Compact device models, BSIM6 model, BSIM-CMG model, BSIM-IMG model, Quantum Transport models -: Tunneling, Schrodinger equation and free particle, potential step, potential barrier, Key issues in MOSFET modeling, Introduction to the TCAD Simulation Tool, Examples of TCAD Simulations

Learning	
Resources	

- Donald Neamen, Dhrubesh Biswas, Semiconductor Physics and Devices, McGraw Hill, 4th ed, 2012.
- 2. S. M. Sze, Physics of Semiconductor Devices, John Wiley, 3rd ed, 2005.
- 3. Pallab Bhattacharya, Semiconductor Opto electronic Devices, 2nd ed, PHI, 2017.
- Nandita Dasgupta and Amitav Dasgupta, Semiconductor Devices: Modelling and Technology Prentice-Hall of India Pvt.Ltd; 1st ed, 2004.
- 5. Dragica Vasileska, Stephen M. Goodnick, Gerhard Klimeck, Computational Electronics, Semiclassical and Quantum Device Modeling and Simulation, CRC Press. 1st ed. 2017.

Learning Asse	essment	/ 6 / ^			7)	0.				
	Bloom's		Continuous Learning	g Assessment (CLA)	A 3	Summative				
	Level of Thinking		Formative	Life-Long	g Learning		al Examination			
		CLA-1	CLA-1 Average of unit test CLA-2				(40% weightage)			
			(50%)							
	9	Theory	Practice	Theory	Practice	Theory	Practice			
Level 1	Remember	20%	E 600 THE WAYNE	20%		20%	-			
Level 2	Understand	20%	The second second	20%	R 794 F	20%	-			
Level 3	Apply	30%	E 100 11 20	30%	Paris.	30%	=			
Level 4	Analyze	30%	1-10 P. 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	30%	1777 7	30%	-			
Level 5	Evaluate			Fe The Market	29 - 12 - E	3	-			
Level 6	Create	F4.1	TWO LAND THE PARTY OF		4 , 4	- 0	-			
	Total	100 %	and the state of the state of	100 %	714 AND 1	100 %				

Course Designers		
Experts from Industry	Experts from Higher Technical Institutions	Internal Experts
1. Mr. Abhijeet Pathak, Western Digital, Bangalore, India.	1. Dr. Kumar Prasannajit Pradhan, IIITDM, Kancheepuram	1. Dr. Aditya Nath Bhat <mark>t, SRMIS</mark> T
	2. Dr GP Mishra, NIT Raipur	2. Dr. Rajesh Agarwal <mark>, SRMIS</mark> T
	17.93	3. Dr. Soumya Ranja <mark>n Routra</mark> y, SRMIST

Course	21ECC533J	Course	ANALOG CIRCUITS AND SYSTEM DESIGN	Course	С	PROFESSIONAL CORE	L	Τ	Р	С
Code		Name		Category			3	0	2	4

Pre-requisite	uisite Nil		Co- requisite		Nil	Progressive	re Nil
Courses		0	Courses			Courses	
Course Offering Department Electronics		Electronics and	d Communicati <mark>on En</mark>	gineering	Data Book / Codes / Sta	ndards	Nil
					- T T T T T T T T T T T T T T T T T T T	Contract Contract	

Course Learning	The purpose of learning this course is to:
Rationale (CLR):	
CLR-1:	understand the operation and design of different MOS amplifier circuits
CLR-2:	emphasize the basics of analog CMOS sub-circuits and its design
CLR-3:	characterize the basics of differential amplifiers and its design analysis
CLR-4:	gain knowledge of various operational amplifiers
CLR-5:	understand and analyse the different oscillator circuits to determine the frequency of oscillation and identify the various components of PLL and its operation

Course	At the end of this course, learners will be able to:		Prog <mark>ram</mark>	o <mark>gramme</mark> Outcomes (PO)			
Outcomes (CO):			1	2	3		
CO-1:	analyse and design of MOS amplifier circuits under various load and understand the frequency response	-	3	2	1		
CO-2:	understand the operation of CMOS current mirrors, biasing circuits and filters	1	3	2	1		
CO-3:	design basic differential amplifiers	7	3	2	1		
CO-4:	understand the operation of Operational amplifiers	7	3	2	1		
CO-5:	elucidate and design oscillator circuits to meet certain specifications and illustrate the function of PLL and its performance		3	2	1		

Module-1 - CMOS Amplifier 15 Hour

Introduction to Analog Design Single stage amplifiers - Common source Amplifier with Resistive load and Diode connected load, Common source amplifier with source Degeneration, Source Follower, Common Gate amplifier, Noise analysis, Frequency response of amplifiers, Multistage Amplifiers- Cascode Amplifier, Folded Cascode amplifier, Noise analysis and frequency response of Cascode stage amplifier.

Practice on Common source amplifiers with different loads. Source follower

Module-2 - Current Mirror and Bandgap reference Sources

15 Hour

General Properties, Basic Current mirrors, Cascode current mirrors, Active Current Mirrors, Block Diagram of Band gap reference circuits, Supply Independent Biasing, Temperature independent Reference circuit, PTAT Current Generation, Constant—Gm biasing.

Practice on of Basic current mirror, Cascode Current mirror, Voltage Reference circuits

Module-3 - Differential amplifier

15 Hour

DC transfer characteristics of source coupled pair, small signal analysis, Single-ended operation and Differential operation, Basic differential pair, Qualitative analysis of differential amplifier, Common-mode response, Differential pair with MOS loads, Frequency response of Differential amplifier, Noise in differential amplifier.

Practice on different configurations of differential amplifiers

Tradition on amorent cornigarations of amorental amplim

Module-4 - Operational Amplifier

15 Hour

Performance parameters of op-amp, Block Diagram, One stage op-amp, Two Stage op-amp, Voltage gain of two stage op-amp, Input common range and output swing, Slew rate, Power supply rejection ratio, Gain Boosting, Frequency response of op-amp, Folded Cascode CMOS op-amp, Voltage gain and frequency response of Folded Cascode op-amp, Rail to rail input operation, Noise in op-amps.

Practice on one stage and two stage operational amplifiers

Module-5 – Oscillators and Phase Locked Loops

Ring oscillator, two stage and three stage ring oscillators, LC oscillators, Cross Coupled oscillator, Voltage controlled oscillators, Tuning range of VCOs, Basic PLL topology and characteristic parameters, Phase detector, Charge Pump PLL, Problem of lock acquisition, non-ideal effects in PLL, Jitter in PLLs, Transient response of PLL in the locked state, Applications of PLL: Frequency multiplication. Case Study: Design of Ring Oscillator for specific practical circuit, Design of VCO for a particular locking frequency Practice on different types of Cross-coupled Oscillator, Colpitts Oscillators and PLL circuit

Learning
Resources

- Gray, Meyer, Lewis, Hurst, "Analysis and design of Analog Integrated Circuits", 5th Edition, Willey International, 2009.
- 2. Allen, Holberg, "CMOS analog circuit design", 3rd Edition, Oxford University Press, 2012
- 3. Behzad Razavi, "Design of analog CMOS integrated circuits", 2nd Edition, McGraw Hill, 2017
- 4. Adel S. Sedra, Kenneth C. Smith, "Microelectronic Circuits" 7th Edition, Oxford University Press, 2015
- 5. Ndjountche, Tertulien," CMOS Analog Integrated Circuits: High-Speed and Power-Efficient Design", 2nd Edition, CRC Press, 2019.

Learning Asse	essment	- A			. ~ ~ ~		
	Bloom's		Continuous Learning	g Assessment (CLA)		Sur	nmative
	Level of Thinking Formative Life-Long Learning		Final Examination				
		CLA-1 Average of unit test CLA-2 (45%) (15%)			(40%)	weightage)	
		Theory	Practice	Theory	Practice	Theo <mark>ry</mark>	Practice
Level 1	Remember	20%	10 mm	No. of Part of the	20%	20%	-
Level 2	Understand	20%	A 10 10 10 10 10		20%	20%	=
Level 3	Apply	30%	Charles And Land	9.78 a 1 34	30%	30%	-
Level 4	Analyze	30%	10 May 1 - 10 May 12		30%	30%	=
Level 5	Evaluate	2.7.77	10 Y X 1 - 1 - 1	 4. Prof. 2014.3 			-
Level 6	Create		Committee of the Committee of		7.5		-
	Total	10	0%	10	0%	1	00 %

Course Designers		
Experts from Industry	Experts from Higher Technical Institutions	Internal Experts
 Mr. Sethupathy Balakrishnan, Lead Application 	1. Prof Meenakshi M, Dept of Electronics and	
Engineer, Cadence Designs Systems.	Communication Engineering, College of Engineering	1. Dr. K. Feren <mark>ts Koni J</mark> iavana, SRMIST
t to the second	Guindy, Anna University	
	2. Prof. Binsu J Kailath, Dept of Electronics Engineering,	2 Dr. I Maniula CDMICT
	IIITDM, Kancheepuram	2. Dr. J. <mark>Manjula, S</mark> RMIST

Course	21ECC534J Course	VLSI PHYSICAL DESIGN AUTOMATION	Course	С	PROFESSIONAL CORE	L	T	Р	С
Code	Name		Category			3	0	2	4

Pre-requisite	Nil	Co- requisite		Nil	Progressive	Nil
Courses		Courses			Courses	
Course Offering	Department Electronics an	d Communication E	ngineering	Data Book / Codes / Stan	dards	Nil
				- 1777		

Course Learning	The purpose of learning this course is to:
Rationale (CLR):	
CLR-1:	learn the VLSI design flow, design styles and design rules along with the basics of graph theory
CLR-2:	discuss the methods of Partitioning and Clustering
CLR-3:	interpret the methods of placement and floor planning
CLR-4:	describe the methods of Routing and layout compaction
CLR-5:	estimate the physical design of FPGA and MCMS

Course	At the end of this course, learners will be able to:	Progran	nme Outcom	es (PO)
Outcomes (CO):		1	2	3
CO-1:	understand the basic concepts of VLSI Physical Design Automation	3	1	1
CO-2:	expose to hierarchical modelling concepts and the necessary knowledge to perform partitioning and clustering algorithms.	3	1	2
CO-3:	design a compac <mark>t IC usin</mark> g floor planning and placement methodologies	2	1	3
CO-4:	analyse the routi <mark>ng proce</mark> ss to achieve the performance of the digital design	3	1	2
CO-5:	design and deve <mark>lop phys</mark> ical design algorithms in optimization of VLSI layout	3	1	2

Module-1 Introduction to VLSI Physical Design Automation

15 Hour

Electronic Design Automation (EDA), VLSI design flow, VLSI design styles, physical design automation, Physical design optimization, Algorithms and complexity, Graph theory terminology- Graph search algorithms- Spanning tree algorithms- shortest path algorithms

Practice on design of functional verification of logic gates. Practice on design of combinational circuits

Module-2 Partitioning and Clustering

Module-4 - Routing

15 Hour

Basic Concepts- Partitioning, Kernighan-Lin, Fiduccia- Mattheyses, Basic Concepts- Clustering - Agglomerative Clustering - Rajaraman and Wong algorithm- Hyper edge coarsening - Modified Hyper edge coarsening - Practice problems in Clustering

Practice on functional verification of Sequential circuit using 90nm Technology using Cadence RTL Compiler (RC) tool.

Practice on Implementation of KL Partition algorithm in 90nm Technology and analyze the implemented circuit and check for the changes in delays, setup and hold times

Module-3 - Compaction, Floor planning and Placement

15 Hour

Compaction and it's aspects in Physical design-1D and 2D compaction-Liao Wong algorithm-Floorplan based design methodologies- Introduction to Floor planning- Slicing and Non slicing floorplan-Polar graphs representation-Sequence-pair-Shape functions- Non-slicing methods: Introduction to Placement - Problem formulation and classification - Enhancement of Min- cut placement - Placement algorithm using Simulated annealing - Placement algorithm using Genetic algorithm

Practice on implementation of FM Partition algorithm in 90nm Technology analyze the implemented circuit and check for the changes in delays, setup and hold times

Practice on analysis of a circuit in the power planning stage using 90nm Technology

Channel routing and terminologies: Global Routing- Problem Formulation- Classification of Global Routing- Maze routing algorithm- Line Probe algorithms- Shortest Path algorithms: Steiner Tree based algorithms- Channel routing-Terminologies-Constraint graphs-Detailed Routing: Problem formulation- Classification of Detailed routing- Two-layer channel routing algorithms: Left Edge algorithm- Dogleg Routing algorithm-Clock tree routing- H-tree algorithm

Practice on Routing and placement Analysis

Practice on pre-Placement analysis in EDA Environment

Module-5 – Practical Design Issues and automation of simulation

15 Hour

Elmore Delay based routing constructions – Physical design techniques in simulation mechanisms- Delay model-Data structures in event driven simulation- Switch level techniques-Partitioning for simulation- Physical Design Automation of FPGAs-Physical design automation of MCMS.

Practice on generation of Clock Tree Synthesis (CTS) of a synchronous circuit using 90nm Technology

Practice on deciding on a final optimum back-end design of a circuit using 90nm Technology

Mini project

Learning	1. Naveed Sherwani, Algorithms for VLSI physical design Automation,	3. Algorithms for VLSI Design Automation-Sabih Gerez-Wiley publishers, 2006.
Resources	Kluwer Academic Publishers, 2010.	4. Sadiq M. Sait, Habib Youssef, "VLSI Physical design automation theory and Practice", World
	Sung Kyu Lim, "Practice Problems in VLSI physical design Automation",	Scientific Publishing, 1999
	Springer, 2008	Article Co. Co. Nation

Learning Asse	ssment					/	
	Bloom's	Continuous Learn	ning Assessment (CLA)	20 10 18 m 1 1 1 1	7 7 7 7	Summa <mark>tive</mark>	
	Level of Thinking	Formative	Formative Life-Long Learning CLA-1 Average of unit test CLA-2		Final Ex <mark>aminatio</mark> n		
		(450()			CLA-2 (15%)		(40% we <mark>ightage</mark>)
		Theory	Practice	Theory	Practice	Theory	Practice
Level 1	Remember	20%		- 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1 - 1	20%	20%	-
Level 2	Understand	20%			20%	20%	-
Level 3	Apply	30%	- 111	11.50	30%	30%	-
Level 4	Analyze	30%	-	17	30%	30%	-
Level 5	Evaluate		-		- / /	- / - /	-
Level 6	Create	A - 1 / N		A 12 10 10 10 10 10 10 10 10 10 10 10 10 10	- /_//	-/ -/	-
	Total	100 %		100 %		1 <mark>00 %</mark>	

Course Designers	/ IX EARN - FAD ID.	n /
Experts from Industry	Experts from Higher Technical Institutions	Internal Experts
Dr. Sandeep Patil, CEO, EspinNanotech	Prof Meenakshi M, Dept of Electronics and	1. Dr. <mark>S.Roji Marj</mark> orie, SRMIST
Solutions, IIT Kanpur	Communication Engineering, College of Engineering	
	Guindy, Anna University	
	2. Prof. Binsu J Kailath, Dept of Electronics Engineering,	2. Mr. M. Maria Dominic Savio, SRMIST
	IIITDM, Kancheepuram	

ACADEMIC CURRICULA

VLSI Design

Professional Elective Courses

Regulations 2021



SRM INSTITUTE OF SCIENCE AND TECHNOLOGY

(Deemed to be University u/s 3 of UGC Act, 1956)

Kattankulathur, Chengalpattu District 603203, Tamil Nadu, India

Course	21ECE531T Cours	CICNAL DECCESSING TECHNIQUES FOR VISI	Course	PROFESSIONAL ELECTIVE	L	Т	Р	С	1
Code	Name	SIGNAL PROCESSING TECHNIQUES FOR VLSI	Category -	PROFESSIONAL ELECTIVE	3	0	0	3	

Pre-re-	quisite //	Co- requisite Courses	Nil	Progressive Courses	Nil
Cours	se Offering Department	Electronics and Communication Engineering	Data Book / Codes / Standards		Nil

Course Learning Rationale (CLR):	The purpose of learning this course is to:
CLR-1:	understand the basic computation item in VLSI Signal Processing.
CLR-2:	familiar with concepts of iteration Bound, Retiming, Folding
CLR-3:	understand the Design Efficient Pipelining filter design
CLR-4:	learn the concept of paralle <mark>l process</mark> ing of FIR filter for low power design
CLR-5:	understand the concept of Bit-level arithmetic architectures

Course Outcomes	At the end of this course, learners will be able to:	Prograi	nme Outcomes (PO)
(CO):	At the cita of this course, real rich will be able to.	1	2	3
CO-1:	understand VLSI design methodology for signal processing systems.	3	2	-
CO-2:	be familiar with VLSI algorithms and architectures of DSP.	2	-	2
CO-3:	be able to implemen <mark>t basic</mark> architectures for DSP using CAD tools.		2	2
CO-4:	design the pipelined and parallel FIR Filter	2	-	3
CO-5:	be familiar with low power design concepts of ASICs and high-speed design		3	2

Module -1 Introduction to DSP System

9 Hour Iteration Bound – data flow graph representations – loop bound – iteration bound – problems on iteration bound techniques - various mechanism for iteration bound computation – Longest path matrix – problems on LPM techniques – pipelining and parallel processing – Introduction pipelining of FIR Digital filter, parallel filter – pipelining processing for low power – parallel processing for low power – problems on low power pipelined and parallel process system. Introduction to retiming – problems on retiming mechanism.

Module -2: Systolic Architecture and Algorithm Strength Reduction

9 Hour

Algorithm strength reduction in filter – Transforms – 2-parallel FIR Filter – 2-parallel Fast FIR Filter – DCT algorithm architecture transformation – parallel architecture for rank order filter - ODD-EVEN merge sorter architecture – parallel rank order filter introdu<mark>ction and</mark> design – problems related to ODD-EVEN merge sort filter – problem on rank order filter – <mark>problem o</mark>n ODD-EVEN merge sort – Systolic architecture design – Introduction – FIR systolic array sample problems

Module- 3- Fast Convolution

9 Hour

Fast convolution – Cook –Toom algorithm –problem – modified cook-toom algorithm – problems- pipeline and parallel recursive and adaptive filter – Inefficient/efficient interleaving architecture – parallel recursive structures - interleaving mechanism – look-ahead pipelining in FIR filter - problem on look-ahead techniques – problems on interleaving – problem on parallel recursive structure – application of lookahead pipelining - clustered Look-ahead pipelining.

Module -4 - Bit-Level Arithmetic

9 Hour

Scaling and round-off noise – scaling operation, round-off noise – state variable description of digital filters – scaling and round-off noise computation – Round-off noise in pipelined first –order filters. Problems on round-off noise computation – Bit-level Arithmetic Architectures- parallel multiplier sign extension – parallel carry-ripple array multiplier – parallel carry-save array multiplier tabular form and implementation – 4x4 bit Baugh Wooley carry save array multiplier and implementation. Operation description of parallel carry save - problems on bit-arithmetic - application study on carry save multiplication.

Module-5 - High Performance Algorithm for ASIC

9 Hour

Numerical Strength Reduction – Sub Expression elimination – Multiple Constant Multiplications – Iterative Matching – Linear transformations-Low power Design Techniques – Introduction to wave pipelining – Asynchronous pipelining bundled data versus dual-rail protocol- wave Pipelining in detail – Asynchronous pipelining – introduction – Detail description on Asynchronous pipelining mechanism – Data vs Dual Rail Protocol – needs for low power VLSI chips, charging and discharging capacitance – CMOS leakage current – basic principles of low power design.

Learning
Resources

- Keshab.K. Parhi, "VLSI Digital Signal Processing Systems: Design and Implementation", Wiley, NY 1999
- 2. Gary Yeap, "Practical Low Power Digital VLSI Design", Kluwer Academic publishers, 1988.
- 3. Mohammed Ismail and Terri Fiez, "Analog VLSI Signal and Information Processing", 1988.
- 4. S. Y. Kung, H.J. White House T. Kailath, "VLSI and Modern Signal Processing", Prentice HALL, 1985.
- Jose E. France, Yannis Tsividis, "Design of Analog & Digital VLSI Circuits for Telecommunication and Signal Processing", Prentice Hall, 1994.

Learning Assessment				_ /				
	Bloom's Level of Thin <mark>king</mark>	Continuous Learning A Formative CLA-1 Average of unit test (50%)			Learning A-2 (%)	Summative Final Examination (40% weightage)		
	/ 2 /	Theory	Practice	Theory	Practice	Theory	Practice	
Level 1	Remember	20%	हा पाना अध्यक्ति । ज	20%		20%	-	
Level 2	Understand	20%	Carlor State Comment	20%		20%	-	
Level 3	Apply	30%	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	30%	. N - 7	30%	-	
Level 4	Analyze	30%	West of Principle All	30%		30%	-	
Level 5	Evaluate		Mary State Section	1 100000	- C	-	-	
Level 6	Create			1777年8月19日代		-	-	
	T <mark>otal = = = = = = = = = = = = = = = = = = =</mark>	10)%	100	0 %	100	0 %	

Course Designers			
Experts from Industry		1	Experts from Higher Technical Institutions Internal Experts
1. Dr. Sandeep Patil, CEO,	EspinNa <mark>notech S</mark> olu	tions, IIT	1. Prof Meenakshi M, Dept of Electronics and Communication Engineering, 1. Dr. J. Selvakumar, SRMIST
Kanpur			College of Engineering Guindy, Anna University
			2.Prof. Binsu J Kailath, Dept of Electronics Engineering, IIITDM,
		U	Kancheepuram

Course	21ECE532T Cours	HADDWADE DECICN AND CODIDTING LANCHACE	Course	Е	PROFESSIONAL ELECTIVE	L	Т	Р	С	
Code	Nam	HARDWARE DESIGN AND SCRIPTING LANGUAGE	Category	E	PROFESSIONAL ELECTIVE	3	0	0	3	

Pre-requ Course	N	il Co-requisite Courses	Nil	Progressive Courses	Nil
Course Offering Department		Electronics and Communication Engineering	Data Book / Codes / Standards		Nil

Course Learning Rationale (CLR):	The purpose of learning this course is to:
CLR-1:	understand the basic features of System C.
CLR-2:	construct the different types of digital systems in System C
CLR-3:	utilize the basic constructs of System Verilog and Identify different types of System Verilog Advanced features.
CLR-4:	understand Assertions in System Verilog.
CLR-5:	construct basic programs in TCL.

Course Outcomes	At the end of this course, learners will be able to:	Prog	ramme Outcomes	(PO)
(CO):	At the cita of this course, real roles with so take to.	- 1	2	3
CO-1:	understand the basic concepts of System C	_ 1	-	1
CO-2:	analyse Combinational and Sequential Circuits in System C	2	2	2
CO-3:	gain knowledge on the basic conventions in System Verilog and System Verilog advanced features.	2	-	2
CO-4:	utilize the Assertion feature in System Verilog	-3	3	2
CO-5:	utilize various concepts in TCL	3	2	2

Module-1 – System C

Introduction to System C, Design Methodology, Data types –Value holders, bit, arbitrary width logic type, Integer type, Resolved type, User-defined type, Modelling combinational logic - SC -module, Reading and writing port signals, Logical operators, Arithmetic operators, Relational operators, Programs using Operators, Vector Ranges, IF statement, Switch statement, Programs using IF, SWITCH Statements, Loops, methods, Structures, Delta delay, Programs on Adder, Multiplexer, Decoder, Encoder, Priority encoder, Modelling flip flops and latches.

Module-2 - Advanced Features of System C

9 Hour

Modeling an FSM-Mealy FSM, Moore FSM, Universal shift register, Counters- Modulo N counter, Johnson counter, Gray code up-down counter, Writing a Test bench, Simulation control, SC-thread process, Dynamic sensitivity, Constructor arguments, Ports, Interfaces and Channels, Shared data members, Fixed point types, Module, Simulation Algorithm, Run time environment

Module-3 - System Verilog 9 Hour

Literal values, Data types- String data type, User-defined types, Enumerations data type, Arrays – Dynamic Arrays, Associative arrays, Data declarations, Attributes, Operators-Assignment, Real, Streaming, conditional, Operator overloading, Procedural statements and Control, Flow Process, Tasks and Functions.

Module-4 - Advanced Features of System Verilog

9 Hour

Classes -Objects, Methods, Static Methods, Casting, Chaining Constructors, Data hiding, Encapsulation, Parameterized classes, Polymorphism, Classes and structures, Random constraints and variables, Randomization methods, Assertions, Boolean expressions, Sequences, Case studies -System Verilog assertion API, System Verilog coverage API.

Module-5 – Scripting Language 9 Hour

TCL Fundamentals, Strings and Pattern Matching, TCL Data Structures-TCL Lists, Arrays, Control Flow Commands, Procedures and Scope, Eval Commands

	1.	J. Bhaskar, "A System C Primer", Star Galaxy publications, 2010. System Verilog for Verification: A Guide to Learning the Test Bench Language Features by Chris	
Learning	۷.	Spear and Greg Tumbush, Springer 3rd Edition, 2012.	
Resources	3.	David C. Black, Jack Donovan, Bill Bunton, Anna Keist, System C: From the Ground Up, Springer	ŀ
		2nd Edition, 2005.	

- 4. System Verilog 3.1 a-Language Reference Manual (Accelera's Extensions to Verilog 2001),2004
- 5. Brent Welch," Practical Programming in TCL and TK," Pearson; 4th Edition, 2003

	Bloom's Level of Thinking	Formative CLA-1 Average of unit test (50%)		CL	g Learning A-2 0%)	Summative Final Examination (40% weightage)		
		Theory	Practice	Theory	Practice	Theory	Practice	
Level 1	Remember	20%	A # 18 M 18	20%		20%	-	
Level 2	Understand	20%	12 5 7 1 1 W	20%		20%	-	
Level 3	Apply	30%	Sec. 2777	30%		30%	-	
Level 4	Analyze	30%		30%		30%	-	
Level 5	Evaluate			3924		-	-	
Level 6	Create	-	A STATE OF THE STA	- 17			-	
	Total	10	0 %	10	0 %	10	00 %	

Course Designers		
Experts from Industry		Experts from Higher Technical Institutions Internal Experts
Mrs. A. Suganya, Sr. Scientist and Head, Hardw	are Security	1. Prof Meenakshi M, Dept of Electronics and Communication 1.Dr. Sudhanya P, SRMIST
Research Group, SETS, Chennai		Engineering, College of Engineering Guindy, Anna University
		2. Prof. Binsu J Kailath, Dept of Electronics Engineering, IIITDM, 2.Mrs. N. Saraswathi, SRMIST
•		Kancheepuram

Course	21ECE533T	Course	I OW-POWER VI SI DESIGN	Course	Е	PROFESSIONAL ELECTIVE	L	Т	Р	С
Code	21000001	Name	LOW-POWER VLSI DESIGN	Category	E	PROFESSIONAL ELECTIVE	3	0	0	3

Pre-requisite Courses	Ni	Co- requisite Courses	<i>-</i>	Nil	Progressive Courses	Nil
Course Offeri	ng Department	Electronics and Communication E	ngineering	Data Book / Codes / Standards		Nil

Course Learning Rationale (CLR):	The purpose of learning this course is to:
CLR-1:	familiarize with the fundamental concepts of Low Power VLSI
CLR-2:	perceive the knowledge of Probabilistic Power Analysis
CLR-3:	introduce the concepts of Circuit and Logic Level Synthesis for Low Power
CLR-4:	explore the concepts of Special Power Reduction Techniques
CLR-5:	understand the concepts of Architectural Level Approaches and Advanced Techniques

Course Outcomes	At the end of this course, learners will be able to:	Program	me Outcomes	(PO)
(CO):	At the end of this course, learners will be able to.	1	2	3
CO-1:	comprehend the fund <mark>amental</mark> concepts of Low Power VLSI	2	-	-
	acquire knowledge o <mark>n Proba</mark> bilistic Power Analysis	2	-	-
CO-3:	circuit and Logic Le <mark>vel Optim</mark> ization of Low Power	3	2	-
CO-4:	gain knowledge on Special Techniques for Power Reduction	2	-	-
CO-5:	develop skills to ex <mark>plore Arc</mark> hitectural-Level Approaches and Advanced Techniques	2	3	-

Module-1 - Introduction to Low Power VLSI

9 Hour

Introduction - Needs for Low Power VLS<mark>I, Charg</mark>ing and Discharging Capacitance, Short Circuit Current in CMOS Circuit- Inverter, Variation with Output Load and Input Signal Slope, CMOS Leakage Current-Reverse Biased PN-Junction, Subthreshold Channel Leakage, Leakage Current in Digital Design, Static Current, Basic Principles of Low Power Design-Reducing Switching Voltage, Reducing Capacitance, Reducing Switching Frequency, Reducing Leakage and Static Current, Low Power Figure of Merits

Module-2 - Probabilistic Power Analysis

9 Hour

Random Logic Signals, Characterization of Logic Signals, Continuous and Discrete Random Signals, Probability and Frequency, Word-level and Bit-level Statistics, Probabilistic Power Analysis Techniques-Propagation of Static Probability in Logic Circuits, Transition Density Signal Model, Propagation of Transition Density, Gate Level Power Analysis using Transition Density, Signal Entropy, Power Estimation using Entropy

Module-3 Circuit Level and Logic Level Synthesis for Low Power

9 Hour

Transistor and Gate Sizing- Sizing an Inverter Cha<mark>in, Sizing for Dynamic Power Reduction and Leakage Power Reduction, Equivalent Pin Ordering, Network Restructuring, Network Reorganization- Transistor Network Partitioning and Reorganization, Adjustable Device Threshold Voltage, Gate Reorganization, Gated Clock FSMs, State Encoding, FSM Partitioning, Bus Encoding- Gray Coding, One Hot Coding, Bus Inversion Coding, To Coding, Precomputation Logic- Condition, Alternate Precomputation Architectures, Design Issues in Precomputation Logic</mark>

Module-4 - Special Techniques for Power Reduction

9 Hour

Power Reduction in Clock Networks- Clock Gating, Reduced Swing Clock, Oscillator Circuit for Clock Generation, Frequency Division and Multiplication, CMOS Floating Node- Tristate Keeper Circuit, Blocking Gate, Low Power Bus, Delay Balancing, Low Power Techniques for SRAM Cell, Memory Bank Partitioning, Case study: Design of a FIFO Buffer

Module-5 – Architectural-Level Approaches and Advanced Techniques

9 Hou

Switching Activity Reduction- Guarded Evaluation, Bus Multiplexing, Glitch Reduction by Pipelining, Parallel Architecture with Voltage Reduction, Voltage Scaling for Low Power-Multilevel Voltage Scaling, Challenges in Multilevel Voltage Scaling, Dynamic Voltage and Frequency Scaling-Latency Overhead, Adiabatic Computation-Complementary Adiabatic Logic, Power Efficiency of Adiabatic Logic, Adiabatic Charging and Amplification, Pass Transistor Logic Synthesis

Learning Resource	1. 2.	Yeap, Gary K. Practical Low Power Digital VLSI Design. Springer Science & Business Media, 2012. 3. Roy, Kaushik, and Sharat C. Prasad. Low-power CMOS VLSI Circuit Design. John Wiley & Sons, 4.	Pal, Ajit. Low-Power VLSI Circuits and Systems. Springer, 2014 Piguet, Christian. Low-Power CMOS Circuits: Technology, Logic design and CAD Tools.
Resource	3	2009.	CRC press, 2018.

Learning Assessme	nt	.00							
			Continuous Learning	g Assessment (CLA)	*. `	Cum	Common of the co		
	Bloom's Level of Thinking	Formative CLA-1 Average of unit test (50%)		Life-Long Learning CLA-2 (10%)		Summative Final Examination (40% weightage)			
		Theory	Practice	Theory	Practice Practice	Theory	Practice		
Level 1	Remember	20%	-	20%		20%	-		
Level 2	Understand	20%		20%	2 - 1	20%	-		
Level 3	Apply	30%	PAGE 1	30%	1/2-	30%	-		
Level 4	Analyze	30%	10 TO 10	30%	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	30%	-		
Level 5	Evaluate	\	A 5 A 3 A 5 A 5 A 5 A 5 A 5 A 5 A 5 A 5			-	-		
Level 6	Create						-		
	Tota <mark>l</mark>	100)%	10	0 %	10	0 %		

Course Designers	A STATE OF THE STA	3 7
Experts from Industry	Experts from Higher Technical Institutions	Internal Experts
1. Mrs. A. Suganya, Sr. Scientist and Head, Hardware Security	1. Prof Meenakshi M, Dept of Electronics and Communication Engineering,	1. Dr. Sukanya Gho <mark>sh, SRM</mark> IST
Research Group, SETS, Chennai	College of Engineering Guindy, Anna University	
	2. Prof. Binsu J Kailath, Dept of Electronics Engineering, IIITDM,	2. Dr. P. Aruna Priy <mark>a, SRMIS</mark> T
	Kancheepuram	
		3. Dr. Soumyaranj <mark>an Routr</mark> ay, SRMIST

Course	21ECE53/IT	Course	RECONFIGURARI E COMPLITING SYSTEMS	Course	Е	PROFESSIONAL FLECTIVE	L	Т	Р	С
Code	21ECE5341	Name	RECONFIGURABLE COMPUTING SYSTEMS	Category		PROFESSIONAL ELECTIVE	3	0	0	3

Pre-requisite Courses	Nii	Co- requisite Courses		Nil	Progressive Courses	Nil	
Course Offering D	Department	Electronics and Communication E	ngineering	Data Book / Codes / Standards		Nil	

THE RESERVE

Course Learning Rationale (CLR):	The purpose of learning this course is to:
CLR-1:	familiarize wide range of reconfigurable hardware
CLR-2:	introduce architecture that enab <mark>les high p</mark> erformance computation as well as the supporting application mapping process.
CLR-3:	ability to understand the computational architectures for FPGA
CLR-4:	explore different Optical reconfigurable architectures.
CLR-5:	focuses on specific, important field-programmable gate array (FPGA) applications, presenting case studies of interesting uses of reconfigurable technology.

Course Outcomes	At the end of this course, learners will be able to:	Programme Outcomes (PO)				
(CO):	At the cite of this course, realities with the able to:	1	2	3		
CO-1:	understand the funda <mark>mentals</mark> of the reconfigurable computing and reconfigurable architectures.	3				
	articulate the design issues involved in reconfigurable computing systems with a specific focus on Field Programmable Gate Arrays (FPGAs) both in theoretical and application levels					
CO-3:	understand both ho <mark>w to arch</mark> itect reconfigurable systems and how to utilize them for solving challenging computational problems.	3				
CO-4:	understand the mod <mark>els for o</mark> ptical systems, algorithms and techniques for high performance applications					
CO-5:	explore important fie <mark>ld-progr</mark> ammable gate array (FPGA) reconfigurable applications through case studies	3	2	2		

Module-1 - Reconfigurable Computing Hardware

9 Hour

Logic- The computational fabric, Logic Elements, Programmability .Array and interconnect, Interconnect Structures, Programmability, Extending Logic Elements, RAM, Flash Memory, Antifuse, Fine-grained, Coarse-grained, RPF integration into traditional computing, Independent Reconfigurable Coprocessor Architecture Processor, RPF Architectures, operating system support for reconfigurable computing, Abstracted Hardware Resources, Flexible Binding, Scheduling, Evolvable FPGA, Artificial Evolution, Evolvable Hardware Digital Platforms

Module-2 - Mapping Designs into Reconfigurable Platforms

9 Hour

Mapping designs into reconfigurable platforms, Structural mapping algorithm, Area oriented, performance driven mapping, power-aware mapping, Integrated mapping algorithms, Simultaneous Logic Synthesis, Integrated Retiming, Placement-driven Mapping, algorithms for heterogeneous resources, Mapping to Complex Logic Blocks, Mapping Logic to Embedded Memory Blocks, Mapping to Macrocells, The FPGA placement, Clustering, simulated annealing, VPR Annealing Algorithms Related Annealing, Algorithms Simultaneous Placement and Routing with Annealing, analytical placement, partition based placement.

Module-3 - Computational Architectures for FPGA

9 Hour

Precision analysis for fixed point computation, Fixed-point number system, Multiple-word length Paradigm, Word length optimization, Analytic Peak Estimation, Distributed arithmetic, DA implementation, Mapping process, Mapping DA onto FPGAs, An application of DA on an FPGA, FPGA implementation of CORDIC processors. Case study: optimized fixed-point arithmetic, Hardware accelerated algorithms, optimized fixed-point arithmetic circuits in custom hardware.

Module-4 - Optical Reconfiguration Model

9 Houi

Optical reconfigurable models, Basic algorithm techniques, Permutation Routing, Binary Prefix Sums, Algorithms for Optical Models, Basic Results, Sorting and Selection, Multiple Addition, Matrix Multiplication, Bit stream Generation Export Hardware, Complexity of Optical Models, Simulating PRAMs Simulating PRAMs example, Equivalence of One-Dimensional Models Relating the PR-Mesh and the LR-Mesh, Relating Two-Dimensional Optical Models Run time reconfigurability, Run time reconfigurability Design and implementation, Run-Time Reconfiguration Basic Concepts, Generic and Specific Problem.

Module-5 – Case Studies of FPGA Applications

9 Hour

SPIHT Image Compression, SPIHT algorithm, SPIHT Coding Engine, Wavelets and the Discrete Wavelet Transform, The SPIHT Coding Phase, The SPIHT Coding Evaluation, Automatic Target Recognition Systems, Automatic target recognition algorithms, ATR implementations, The Implications of Floating Point for FPGAs, General Implementation Considerations of Adder and their types of Adder, Multiplier

Implementation. Case study: Floating-point unit module – Xilinx Virtex-II Pro (or) ZYNQ XC 7Z020-1CLG400C – 650 MHZ ARM Cortex A9 dual core Processor, Implementation of PYNQ-Z2 -Python languages and libraries

Learning Resources	Scott Hauck and Andre` DeHon, "Reconfigurable Computing: The Theory and Practice of FPGA-Based Computation", Morgan Kaufmann, 2008.	3. Ramachandran Vaidhyanathan and Jerry. L. Trahan "Dynamic Reconfiguration: Architectures and Algorithms", Kluwer Academic publishers, 2003.
	2. Clive Maxfield, "The Design Warrior's Guide to FPGAs: Devices, Tools and Flows",	
	Newnes, Elsevier, 2006	

			Continuous Learning Assessment (CLA)			0	
	Bloom's Level of Thinki <mark>ng</mark>	Forma CLA-1 Averag (50%	e of unit test	CL	g Learning A-2 0%)	Final Ex	mative camination reightage)
	4.37	Theory	Practice	Theory	Practice	Theory	Practice
Level 1	Remember	40 %		40 %	(-/	30 %	-
Level 2	Understand	40 %	F141 48-342 (F4)	40 %		40 %	-
Level 3	Apply	20 %	Mark Tale	20 %		30 %	-
Level 4	Analyze		C 201 1 2 10 10 10 10 10 10 10 10 10 10 10 10 10	- 1	7	-	-
Level 5	Evaluate	A	Block to the section in	8	A		-
Level 6	Create	3 - 30/74		7 M 12 M 14		-	-
	T <mark>otal</mark>	100	%	100	0 %	10	00 %

Course Designers		
Experts from Industry	Experts from Higher Technical Institutions	Internal Experts
1. Mr. Anuj Kumar, Bombardier Tra <mark>nsporta</mark> tion, Ahmedabad,	1. Prof Meenakshi M, Dept of Electronics and Communication	1. Dr. T S Karthik, SRMIST
kumaranuj anii@gmail.com	Engineering, College of Engineering Guindy, Anna University	
2. Mr. Hariharasudhan - Johnson Controls, Pune,	2. Prof. Binsu J Kailath, Dept of Electronics Engineering, IIITDM,	2. Dr. P Aruna P <mark>riya, SR</mark> MIST
hariharasudhan.v@jci.com	Kancheepuram	1 19 1

Course	21FCF535T	Course	CRYPTOGRAPHY AND HARDWARE SECURITY IN VLSI	Course	E	PROFESSIONAL ELECTIVE	L	T	Р	С
Code	212023331	Name	CRIFTOGRAPHT AND HARDWARE SECURITI IN VESI	Category		PROFESSIONAL ELECTIVE	3	0	0	3

Pre-requisite	N			Nil	Progres		Nil
Courses		Courses			Cours	es	
Course Offering	Department	Electronics and Communication E	n <mark>gineeri</mark> ng	Data Book / Codes/Standards	J		Nil

Course Learning	The purpose of learning this course is to:
Rationale (CLR):	The purpose of rearning this course is to.
CLR-1 :	apply mathematical technique <mark>s to crypto</mark> graphy
CLR-2 :	describe principles, techniques and algorithms with a strong desire to learn cryptography
CLR-3:	understand the overview of hardware security algorithms in VLSI
CLR-4:	explore the significance of hardware FPGA
CLR-5:	analyse various attacks and counter measures

Course Outcomes (CO):	At the end of this course, learners will be able to	Ž		Progr	am Outcomes	\$ (PO)
outcomes (co).				1	2	3
CO-1 :	understand the detail <mark>ed math</mark> ematical concepts for cryptography.		-	3	3	1
CO-2 :	describe the general structure of Block cipher and steam cipher algorithms.			3	1	-
CO-3:	analyze performance and hardware Implementation of Hash and RSA			3	3	2
CO-4:	describe variety of state-of-the-art applications such as physically unclonable functions			3	1	-
CO-5:	explore different types of Trojan and physical attacks.	4)		3	2	-

Module-1-Mathematics of Cryptography

Basic concepts in number theory and finite fields: Modular arithmetic- Euclidean Algorithm - Extended Euclidean Algorithm-Fermat's and Euler's Theorem-Groups, Rings and Fields-Finite fields of the form-Mapping between Binary and Composite Fields-Prime Number Generation-Pseudo random Sequence Generator- Linear Feedback shift registers.

Module-2-Modern Cryptography

Security goals-Attacks and Services, Block Ciphers, Feistel cipher, Cipher block chaining mode, Cipher feedback mode, DES - AES algorithms and its key generation-RSA algorithm- Elliptic curve -Hash function--MAC-Steam Ciphers using LFSR

Module-3-Hardware Implementation of Hash Function, RSA

9 Hour

9 Hour

9 Hour

Introduction to Cryptographic Hash Functions-The Merkle-Damgard model of hash functions-Construction of Hash Function-Application of Hash function-Hardware Implementation of Hash Functions-MD5-Pipeling-SHA-2 Performance analysis-SHA-3 Keccak Algorithms, RSA Implementation and security - Hardware implementation of 3-bit multiplier, Serial Parallel multiplier.

Module-4-Security Based on Physical Unclonable Function and FPGA Implementation

9 Hour

Classification of PUF- Weak - ICID - SRAM Based PUFs- NOR& NAND circuit-Strong PUF-Features of strong PUF-Arbiter PUF-Analog PUFs-Glitch PUF architecture- Controlled PUF - FPGA synthesis flow-vulnerabilities-Side channel attack-Fault injection attack-FPGA Implementation of PUFs-Arbiter based PUF-Delay Based PUF.

Module-5-Hardware Trojan and Physical Attacks and its Counter Measures

Taxonomy of Hardware Trojans- Classification-Phase of Insertion- Abstraction level of description-Activation mechanism-effects-Location-Hardware Trojan Detection-Introduction-Hardware Trojan detection in IC-Hardware Trojan detection approaches-Trojan Modelling-Combinational Modelling-Sequential Modelling-Design of MOLES Trojan- Side Channel Attacks-Countermeasures.

	1. Stallings, W. (2020). Cryptography and network security, 8th edition Pearson Education	n 3.Tehranipoor, M., & Wang, C. (Eds.). (2011). Introduction to hardware security and trust. Springer
Learning	India.	Science & Business Media.
Resources	2. Katz, J., Menezes, A. J., Van Oorschot, P. C., & Vanstone, S. A. (1996). Handbook	of 4.Mukhopadhyay, D., & Chakraborty, R. S. (2014). Hardware security: design, threats, and safeguards.
	applied cryptography. CRC press.	Chapman and Hall/CRC.

rning Assessme	nt			CH I				
			Continuous Learning	g Assessment (CLA)	g Learning		mative	
Bloom's Level of Thinking		CLA-1 Average of unit test (50%)		C	LA-2 (0%)	Final Examination (40% weightage)		
	48	Theory	Practice	Theory	Practice	Theory	Practice	
Level 1	Remember	20%	A	20%	7.5	20%	=	
Level 2	Understand	20%	45.00	20%		20%	-	
Level 3	Apply	30%	The second of	30%	-	30%	-	
Level 4	Analyze	30%		30%		30%	-	
Level 5	Evaluate		A 120 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1		7		-	
Level 6	Create		Carlot Comment St.	8. 1 -0 77	11 A - A-1		-	
	Total -	10	00 %	10	00 %	10	0 %	

Course Designers			
Experts from Industry	E	Experts from Higher Technical Institutions	Internal Experts
1. Mrs. A. Suganya, Sr. Scientist and Head, Hardv Research Group, SETS, Chennai		1. Prof Meenakshi M, Dept of Electronics and Communication Engineering, College of Engineering Guindy, Anna University	1. Dr. P. Radhik <mark>a, SRM I</mark> ST
	2	2. Prof. Binsu J Kailath, Dept of Electronics Engineering, IIITDM, Kancheepuram	2. Dr. M. Valar <mark>mathi, SR</mark> M IST
	()		3. Dr. P. Aru <mark>na Priya,</mark> SRM IST

Course	21ECE536T	Course	INTEGRATED NANO-PHOTONICS	Course	_	PROFESSIONAL ELECTIVE	L	Т	Р	С
<u>Code</u>	21ECE5361	Name	INTEGRATED NANO-FITOTONICS	Category	E	PROFESSIONAL ELECTIVE	3	0	0	3

Pre-requisite Courses	Ni	Co- requisite Courses		Nil	Progressive Courses	Nil
Course Offeri	ng Department	Electronics and Communication E	ngineering	Data Book / Codes / Standards		Nil

Course Learning Rationale (CLR):	The purpose of taking this course is to:
CLR-1:	outline the fundamentals of Optics and Photonics
CLR-2:	understand the effect of nano-size on the optical properties of materials
	get familiar with the nanophotonic materials and devices
CLR-4:	understand the concept of metamaterial and metasurfaces
CLR-5:	explore the application of nano-photonics in various fields.

Course Outcomes	At the end of this course, learners will be able to:	Programme Outcomes (PO)				
(CO):	At the end of this course, learners will be able to.	1	2	3		
CO-1:	define basic principle <mark>s and co</mark> ncepts of optics and electromagnetic theory.	3	2	-		
CO-2:	illustrate optical conf <mark>inement</mark> and the effect of device size on its optical properties.	3	2	-		
CO-3:	utilize the optics an <mark>d quantu</mark> m mechanics to understand the concept of nanophotonic.	3	-	2		
CO-4:	acquire knowledge of metamaterial and metasurfaces.	3	2	-		
CO-5:	analyse the nanoph <mark>otonic d</mark> evices for various applications.	2	-	3		

Module-1 - Introduction to Photonics

9 Hour

Basic principles of optics and light propagation, Electromagnetic theory and Maxwell's equations, Wave-particle duality of light, Reflection and refraction, Polarization of light, Interference, and diffraction of light, Coherence, Fresnel equations; Absorption, dispersion, and scattering of electromagnetic waves, diffraction limit – Breaking through the diffraction limit.

Module-2 - Foundations for Nanophotonics

9 Hour

Photons and Electrons: Similarities and Differences, Confinement of photons and electrons, Tunneling, Localization under periodic potential, Nanoscale optical interactions, Nanoscale confinement of electronic interactions, Near-field optics, Modeling near-field nanoscopic interactions, Near-field study of quantum dots, Nano-scale enhancement of optical interactions, Principles of operations of nanophotonic devices using optical near fields.

Module-3 – Nanophotonic Materials and Devices

9 Hou

Quantum Confined Materials: Quantum Wells, Quantum Wires, Quantum Dots, Quantum Rings, Manifestations of Quantum Confinement: Optical Properties, Nonlinear properties, Quantum confined Stark effect, Dielectric confinement effect, Metallic Nanoparticles and Nano-shells, Optical properties of Metallic Nanoparticles, Nanocomposite, Optical properties of Nanocomposites, Photonic Crystals: Basic concepts and features.

Module-4 – Metamaterial and Metasurfaces 9 Hour

Metamaterials concept; Effective medium theories: Maxwell–Garnett theory, Bruggeman theory, Single and Double-Negative metamaterials; Applications: Perfect absorbers; Super lens, Hyperbolic metamaterials and Hyper lens; Tunable photonic metamaterial-based devices; Introduction to metasurfaces; Frequency selective surfaces; Guided mode resonances (GMR); Applications of metasurfaces and GMR based devices; Perfect control over transmission and reflection using metasurfaces

Module-5 – Applications of Nanophotonic Devices

9 Hour

Nano-photonic Devices as Electronic Switches: AND Gate, NOT Gate; Nanocomposite as waveguides, Random Lasers, Quantum confined Lasers; Silicon Photonics: Directional Coupler (DC), Multi-Mode Interferometric Coupler (MMIC). Mach-Zehnder Interferometer (MZI) and Microring Resonator (MRR), Thermo-Optic and Electro-Optic Switches; Reconfigurable Filters and Tunable Delay Lines, Concept of Field Programmable Photonic Gate Array (FPPGA); Biotechnology: Semiconductor quantum Dots for bio-imaging and biosensing.

Learning Resources
Resources

- Nanophotonics, Paras. N. Prasad, New Jersey, USA: John Wiley & Sons Inc., 2004.
 Principles of Nanophotonics, Motoichi Ohtsu, Kiyoshi Kobayashi, Tadashi Kawazoe, Takashi 6. Yatsui and Makoto Naruse, New York, USA: CRC Press-Taylor & Francis Group, 2008.
- 3. Fundamentals and Applications of Nanophotonics. by Joseph W. Haus (2016).
- 4. Introduction to Nanophotonics, Sergey V. Gaponenko, Cambridge University Press (2010).
- Optics, A Ghatak, Tata McGraw-Hill (2009).
- Nanophotonics, Hervé Rigneault, Jean-Michel Lourtioz, Claude Delalande, Ariel Levenson, Wiley-ISTE (2006).
- 7. Optical Metamaterials: Fundamentals and Applications, W. Cai and V. Shalaev Springer (2010)

earning Assessme	ent			THE PARTY OF			
			Continuous Learnin	g Assessment (CLA)		Cum	mative
	Bloo <mark>m's</mark> Level of <mark>Thinking</mark>	Forma CLA-1 Averag (50%	e of unit test	CL	n Learning A-2 0%)	Final Ex	nauve amination eightage)
		Theory	Practice	Theory	Practice	Theory	Practice
Level 1	Remember	15%	The Control of the	15%		15%	-
Level 2	Understand	25%		20%		25%	-
Level 3	Apply	30%	The same and the North	25%		30%	-
Level 4	Analyze	30%		25%	(30%	-
Level 5	Evaluate		The state of the s	10%			-
Level 6	Create		- 107	5%	-4	-	-
	Total	100	%	100	0 %	10	0 %

Course Designers	- (21)	
Experts from Industry	Experts from Higher Technical Institutions	Internal Experts
Mr. Anuj Kumar, Bombardier Transportation, Ahmedabad, kumaranuj.anii@gmail.com	 Dr. Meenakshi, Professor of ECE, CEG, Anna meena68@annauniv.edu 	University, 1.Dr. Sanj <mark>ay Kumar</mark> Sahu, SRMIST
2. Mr. Hariharasudhan - Johnson Cont <mark>rols, Pun</mark> e, <u>hariharasudhan.v@jci.com</u>	2	2. Dr. <mark>Sayantani</mark> Bhattacharya, SRMIST

Course	21FCF537T	Course	TESTING OF VLSI CIRCUITS	Course	_	PROFESSIONAL ELECTIVE	L	Т	Р	С
Code	21ECE3371	Name	TESTING OF VESI CIRCUITS	Category		FROFESSIONAL ELECTIVE	3	0	0	3

Pre-requisite Courses		Nil	Co-requisite Courses		Nil	٠.,	Progressive Courses	Nil
Course Offering	Department	Electronics and Com	imun <mark>ication Engin</mark>	eering	Data Book / Codes/Standards			Nil

Course Learning	The purpose of learning this course is to:	
Rationale (CLR):		
CLR-1:	understand the level in the domain of VLSI Design and Test.	
CLR-2:	learn the concept of VLSI Testing for combinational circuits	
CLR-3:	gain Knowledge of Test generation for sequential circuits	
CLR-4:	introduce Testable me <mark>mory des</mark> ign and IDDQ Testing	
CLR-5:	understand design fo <mark>r testabi</mark> lity	

Course Outcomes	At the end of this course, learners will be able to		Program Outcomes (PO)				
(CO):			_ 1	2	3		
CO-1 :	apply the knowle <mark>dge in th</mark> e domain of VLSI Design and Test	-	3	-	3		
CO-2 :	develop Test generation for combinational circuit		3	-	3		
CO-3:	understand Tes <mark>t generat</mark> ion for sequential circuit and design testable sequential circuit	(3	-	3		
CO-4 :	summarize Testable memory design and IDDQ Testing method		3	2	3		
CO-5:	introduce the de <mark>sign for t</mark> estability and the principle of BIST		3	-	3		

Module-1- Introduction to Testing 9 Hour

Introduction to testing, Role of testing in VLSI Design flow, testing at different Levels of abstraction, Types of testing, Fault Error, defect, diagnosis, yield, Types of testing, Rule of Ten, Defects in VLSI Chip, DC and AC parametric tests, Fault modeling, Stuck-at fault, bridging fault, stuck on open fault in CMOS, fault equivalence, fault dominance and fault collapsing. Fault simulation, Types of fault simulation.

Module-2- Test Generation for Combinational Circuit

9 Hour

Test generation basics, Test generation algorithms, path sensitization and example, Boolean difference and example, Significant Combinational ATPG Algorithm, Dalgorithm, Dalg

Module-3- Test Generation for Sequential Circuits

9 Hour

Testing generation of sequential circuits, Testing of sequential circuits as iterative combinational circuits, state table verification, Test generation based on circuit structure, Design of testable sequential circuits, Controllability and Observability, Ad Hoc design rules for improving Testablity, The scan-path Technique for Testable Sequential circuit design, Boundary scan-Motivation, System configuration with boundary scan, Testable sequential circuit design example. Test Sequence generation using State table. ATPG for synchronous circuit

Module-4- Memory, IDDQ Testing

9 Hour

Testable memory design, Memory organization, RAM fault models, test algorithms for RAMs, GALPAT, walking 0s and 1s, March and Checkerboard Test, IDDQ testing-Motivation, Fault Detected by IDDQ test, IDDQ Testing Methods, limitations of IDDQ testing, Delay faults, Delay test Problem, Path Delay Test, Delay Test Methodologies, Practical considerations in Delay Testing, Cache RAM chip testing, Functional ROM Chip testing. Scan Chain Trace Rules- master, slave, shadow, copy, or extra. Built in self-Memory repair - BIRA, BISR, Efuse

Module-5- Design for 9 Hour Testability

Basic principle of of Built-in Self-Test, Test pattern generation of Built-in Self-Test, Logic BIST, XLBIST Exhaustive Testing, Pseudo- Exhaustive pattern Generation, Pseudo-Random Pattern Generation, Deterministic Testing, Output response analysis, Transition count, Syndrome checking, signature analysis, BIST architectures, BILBO, Memory BIST CMOS Testing, testing of static CMOS circuit, Testing of dynamic CMOS circuit, Design for robust testability.

Testing standards-JTAG (IEEE 1149.1), iJTAG (IEEE 1687), IEEE 1500. On-chip Clock Controllers (OCC)

	T.P. N. Lala, Digital Circuit Testing and <mark>Testablilty , A</mark> cademic Press, 2002.	4. I.M.Abramovici,M.A. <mark>Breuer and</mark> A.D.Friedman, Digital system and Testable design , Jaico
Learning	2.Laung-Terng Wang, Cheng-Wen Wu and Xiaoqing Wen, "VLSI Test Principles and Architectures",	Publishing House 2001
Resources	Elsevier, 2017	5. Zainalabe Navabi, "Digital System Test and Testable Design: Using HDL Models and
Resources	3. Michael L. Bushnell and Vishwani D. Agrawal, "Essentials of Electronic testing for Digital, Memory	Architectures", Springer, 2010.
	& Mixed-Signal VLSI Circuits", Kluwer Academic Publishers, 2017.	

earning Assessm									
	Bloom's Level of T <mark>hinking</mark>	Level of Thinking CLA-2		Formative Life-Long Learning CLA-1 Average of unit test CLA-2		CLA-1 Average of unit test CLA-2		Summative Final Examination (40% weightage)	
		Theory	Practice	Theory	Practice	Theory	Practice		
Level 1	Remember	20%	ALC: NO SERVICE SERVICES	20%		20%	=		
Level 2	Understand	20%	William Party Str.	20%	Ć	20%	=		
Level 3	Apply	30%		30%		30%	-		
Level 4	Analyze	30%	Hart 1997	30%	- L_	30%	-		
Level 5	Evaluate		The same of the sa				-		
Level 6	Create		AND THE RESERVE	1 3 A. L. S.)	-	=		
	Tot <mark>al</mark>	1	00 %	10	0 %	10	0 %		

Course Designers		
Experts from Industry	Experts from Higher Technical Institutions	Internal Experts
1.Dr. Sandeep Patil, CEO, EspinNanotech Solutions, IIT Kanpur	Prof Meenakshi M, Dept of Electronics and Communication Engineering, College of Engineering Guindy, Anna University	1. Dr. V. SARADA, SRMIST
	Prof. Binsu J Kailath, Dept of Electronics Engineering, IIITDM, Kancheepuram	

Course	Course 21ECE538T	Course	HIGH PERFORMANCE ASIC DESIGN	Course	Е	PROFESSIONAL ELECTIVE	L	Т	Р	С
Code	21505301	Name	HIGH PERFORMANCE ASIC DESIGN	Category		PROFESSIONAL ELECTIVE	3	0	0	3

Pre-requisite Courses	Nil		Co- requisite Courses	•••	Nil	Progressive Courses	3.	Nil
Course Offer	ing Department	Electronics a	nd Comm <mark>unication En</mark>	gineering	Data Book / Codes / Standar	is	Nil	

Course Learning	The purpose of learning this course is to:	V
Rationale (CLR):		
CLR-1:	prepare the student to be an entry-level industrial standard ASIC or FPGA designer.	
CLR-2:	give the student an understanding of basics of System on Chip and Platform based design.	
CLR-3:	understand the basic FPG <mark>A Archite</mark> cture	
	analyze the partitioning and placement issues	
CLR-5:	prepare the student to be an entry-level industrial standard ASIC or FPGA designer.	

Course Outcomes	At the end of this course, learners will be able to:		Progra	amme Outcomes (PO)	
(CO):	At the end of this course, learners will be able to.	1	1	2	3
CO-1:	be familiar with diffe <mark>rent FPG</mark> A Architecture and their interconnect mechanism		3	2	-
CO-2:	understand the sign <mark>ificance</mark> of Partitioning and placement in ASIC Design		2	-	3
CO-3:	be familiar with opti <mark>mization</mark> algorithms in ASIC		3	-	1
CO-4:	strong foundation in various routing algorithm	L	2	2	-
CO-5:	detail analysis of clo <mark>ck plann</mark> ing in ASIC		1 -	-	2

Module-1- Introduction To ASIC 9 Hour

Types of ASICs -VLSI Design flow- Programmable ASICs design types-Antifuse, SRAM- EPROM based ASICs - ASIC Fusing based on EPROM -EEPROM based ASICs -FAMOS description- Programmable ASIC logic cells-ASIC I/O cells -Introduction to CPLD -Types of CPLD.

Module-2-Programmable ASIC Logic Cells 9 Hour

Actel ACT Architecture -Actel Interconnect delay analysis -Xilinx LCA -Architecture -Xilinx EPLD Architecture-Xilinx LCA Interconnect-Xilinx EPLD Interconnect-Altera MAX 5000 - Architecture and interconnect-ASIC Design system: Introduction-Design Systems: Detailed analysis.

Module-3-Optimization Methods

9 Hour

Trade off issues at System Level -Solutions to the issues at system level -Optimization about speed, area and power -Optimization trade-off factor -Asynchronous and low power system design-ASIC physical design issues.

Module -4 -System Partitioning

9 Hour

System partitioning: Objectives -System partitioning Procedure-Objective of System Portioning - Partitioning methods- Measuring Connectivity - Problem on Constructive Partitioning - Constructive Partitioning Interative Partitioning Improvement - Problem on Iterative Partitioning Improvement - The Kernighan-Lin Algorithm - The Ratio-Cut Algorithm.

Module-5-Routing

9 Hour

Introduction to Routing-Global and Local Routing- Introduction to Left Edge First Algorithm -bend minimization technique-over the cell (OTC) Routing -Transistor chaining -min-cut placement algorithm with problems- Clocking strategies -1D compaction

Learning Resources	1. Douglas J. Smith, HDL Chip Design, Madison, AL, USA: Doone Publications, 1996. 2. Jose E. France, YannisTsividis, "Design of Analog - Digital VLSI Circuits for Telecommunication and Signal Processing", Prentice Hall, 1994. 3. M.J.S.Smith, "Application - Specific Integrated Circuits", Pearson, 2003
l .	

ning Assessme		•	0 "					
	Bloom's Level of Thinking	Formative CLA-1 Average of unit test (50%)		CL	g Learning LA-2 0%)	Summative Final Examination (40% weightage)		
	/ 6	Theory	Practice	Theory	Practice	Theory	Practice	
Level 1	Remember	20%	10 P. F. F. S. G.	20%		20%	-	
Level 2	Understand	20%	10 July 1777	20%		20%	-	
Level 3	Apply	30%		30%	- C- Z	30%	-	
Level 4	Analyze	30%	ALTERNATION OF	30%		30%	-	
Level 5	Evaluate	-	Charles To the Control	- No. of		-	-	
Level 6	Create		A 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1		. 3 - 7	-	-	
	Total	1	00 %	10	00 %	100	0 %	

Course Designers	H	경기에게 하다 그런 것이 없는 것이다. 함께 20년 전략다는데	
Experts from Industry	Exp	erts from Higher Technical Institutions	Internal Experts
1. Mrs. A. Suganya, Sr. Scientist and H <mark>ead, Ha</mark> rdware Security	y 1.	Prof Meenakshi M, Dept of Electronics and Communication	1. Dr. J. Selvakumar <mark>, SRMIST</mark>
Research Group, SETS, Chennai		Engineering, College of Engineering Guindy, Anna University	
	2.	Prof. Binsu J Kailath, Dept of Electronics Engineering, IIITDN	, <mark>2. Dr. R. Prithiviraj, <mark>SRMIST</mark></mark>
		Kancheepuram	

Course	21ECE530T	Course	OLIANTUM COMPLITATION AND ALGORITHMS	Course	 DDOEESSIONAL ELECTIVE	L	Т	Р	С
Code	21505331	Name	QUANTUM COMPUTATION AND ALGORITHMS	Category	PROFESSIONAL ELECTIVE	3	0	0	3

Pre-requisite Courses	Ni	,	•••	Nil	Progressive Courses	Nil
Course Offeri	ng Department	Electronics and Communication Engir	neering Data B	ook / Codes / Standards		Nil

Course Learning Rationale (CLR):	The purpose of learning this course is to:
CLR-1:	explore quantum computing and its underlying principles in quantum mechanics.
CLR-2:	analyze quantum circuits fo <mark>r comput</mark> ational tasks.
CLR-3:	utilize the open-source Qiskit platform for quantum programming.
CLR-4:	study the grover and deutsch-jozsa quantum algorithms for solving specific problems efficiently.
CLR-5:	investigate the practical applications of quantum concepts across various fields.

Course Outcomes	At the end of this course, learners will be able to:	9	Progra	mme Out (PO)	comes
(CO):		-	1	2	3
CO-1:	understand fundamental concepts in quantum computing and quantum algorithms.		3	2	3
CO-2:	design and analyze quantum circuits for various computational tasks.		3	2	3
CO-3:	apply quantum computing principles to machine learning problems.		3	2	3
CO-4:	implement and optimize quantum algorithms for efficient problem-solving.		3	2	3
CO-5:	interpret variational circuits as machine learning models and apply them effectively.		3	2	3

Module-1 - Quantum Computing Fundamentals

9 Hour

Introduction to Quantum Computing: Need for Quantum Computing and fundamental concepts - Vector spaces, Probability, Complex numbers, and mathematical preliminaries - Postulates of quantum mechanics - Bra-ket notations - Measurements, Composite systems, Quantum States and Entanglement: Bell's state, Entanglement - Bloch sphere, Pure and Mixed states

Module-2 - Quantum Gates and Circuits

9 Hour

Quantum Gates and Superposition: Quantum superposition - Qubits: What is a Qubit? Mathematical Representation - Bloch Sphere and Quantum Gates - Entanglement and Multi-Qubit states - CNOT gate, Quantum Circuits and Complexity: Geometry of quantum states - Quantum gates, Quantum circuits - Quantum circuit design

Module-3 - Quantum Algorithms

э поиг

Quantum Circuit Analysis: Quantitative measures of circuits - Analysis of the quality of circuits - Circuit optimization. Quantum Algorithms: Introduction to Grover's algorithm - Detailed walkthrough on Grover's algorithm - Grover's search applied to an unstructured database - Quantum Teleportation, Shor's algorithm, Quantum Fourier Transform - Deutsch Algorithm, Deutsch-Jozsa algorithm

Module-4 - Quantum Computing and Machine Learning

9 Hour

Introduction to Quantum Machine Learning - Parameterized <mark>quantum circu</mark>its (PQC) - Quantum Information Encoding - Training parameterized quantum circuits - Quantum Support Vector classification (QSVM)-Examples of Typical Machine Learning Problems - The Three Ingredients of a Learning Problem – Data -Model – Loss - Risk Minimisation in Supervised Learning - Minimising the Empirical Risk as a Proxy -Quantifying Generalisation – Optimisation - Training in Unsupervised Learning - Methods in Machine Learning - Linear Models - Neural Networks- Graphical Models - Kernel Methods

Module-5 - Variational Circuits as Machine Learning Models

9 Hour

How to Interpret a Quantum Circuit as a Model - Deterministic Quantum Models - Probabilistic Quantum Models - An Example: Variational Quantum Classifier - An Example: Variational Generator- which Functions Do Variational Quantum Models Express? - Quantum Models as Linear Combinations of Periodic Functions - An Example: The Pauli-Rotation Encoding-Training Variational Quantum Models - Gradients of Quantum

Computations - Parameter-Shift Rules - Barren Plateaus - Generative Training- Quantum Circuits and Neural Networks - Emulating Nonlinear Activations - Variational Circuits as Deep Linear Neural Networks - Time-Evolution Encoding as an Exponential Activation.

Learning Resources	Nikio Nakahara and Tetsuo Ohmi, "Quantum Computing", CRC Press, 2008 Nakahara and Tetsuo Computer Science", Cambridge, 2007. N. David Mermin "Quantum Computer Science", Cambridge, 2007.	8. Quantum Cryptography. D. Unruh:, Available online: https://courses.cs.ut.ee/all/MTAT.07.024/2017_fall/uploads/ 9. NIST Post Quantum Cryptography, Available online: https://csrc.nist.gov/projects/post-quantum-cryptography/round-2-submissions
-----------------------	---	---

Learning Assessmer	nt		, : Alle 10	14				
	/ 3 /		Continuous Learnin	Common et is a				
	Bloom's Level of Th <mark>inking</mark>	CLA-1 Avera	native ge of unit test 0%)	Life-Long CL/ (10	4-2	Summative Final Examination (40% weightage)		
		Theory	Practice	Theory	Practice	Theory	Practice	
Level 1	Remember	30%	A STATE OF THE STA	30%		30%	-	
Level 2	Understand	30%	100 100 may 100 100	30%		30%	=	
Level 3	Apply	20%	All Control of the Control	20%	- C	20%	-	
Level 4	Analyze	10%	17 July 1985	-10%		10%	=	
Level 5	Evaluate	10%	W 2017 1 2 1	10%	S -	10%	-	
Level 6	Create	47,-2-	The same and N			-	-	
	To <u>tal</u>	10	0 %	100) %	100	%	

Course Designers	17.00	W 4 2
Experts from Industry	Experts from Higher Technical Institutions	Internal Experts
1. Mrs. A. Suganya, Sr. Scientist and Head, Hardware Security	Prof Meenakshi M, Dept of Electronics and Communication Findings of Engineering Culinds Appa University	1 Dr. B. Drithiuiroi CDMIST
	Prof. Binsu & Kallath, Dept of Electronics Engineering, IIITDM, Kacebeanurum	2 Dr. Coupthri SPMIST
	Kancheepuram	Z. Dr. Gayattii, Skiviis i

Course	21ECE631T	Course			Е	PROFESSIONAL ELECTIVE	L	T	Р	С
Code		Name		Category			3	0	0	3

Pre-requisite Courses	21ECC533J, 21ECE531	1T		Co-requisite Courses	Nil		Progressive Courses	Nil
Course Offering	Department Electi	tronics and Co <mark>mmunication</mark> Engii	neering	Data Book / Co	odes / Standards	à l	* T	Nil

Course Learning	The purpose of taking this course is to:
Rationale (CLR)	
CLR-1	understand the challenges involved in analog design and the necessity of Mixed Analog-Digital (MAD) chips.
CLR-2	explore the design and implementation of nonlinear analog circuits and understand their applications in mixed-signal IC design.
CLR-3	learn the principles and characteristics of continuous-time and discrete-time filters and understand their applications in signal processing.
CLR-4	explore different DAC and ADC architectures, along with their specifications and trade-offs.
CLR-5	comprehend the basic architecture and applications of PLLs in electronic systems.

Course Outcomes (CO)	At the end of this course, learners will be able to		Program comes (l	
		1	2	3
CO-1	identify and articulate the advantages of MAD circuits over traditional analog circuits.	0	1	0
CO-2	design and an <mark>alyze co</mark> mparators and sample-and-hold circuits based on specific design requirements.	1	2	3
CO-3	design and analyze active RC filters, MOSFET-C filters, and Switched-Capacitor (SC) circuits.	2	2	3
CO-4	analyze quantization noise and design various DAC and ADC architectures, considering factors such as speed, accuracy, and power consumption.	3	2	3
CO-5	design PLL-based electronic oscillators and frequency synthesizers for different applications; integrate BIST structures into PLL designs, enhancing their reliability and	3	2	3
	testability.			

Module-1: Introduction to Analog and Mixed Signal Design

3 Hour

Challenges in analog design, Need for Mixed Analog-Digital (MAD) chips, Mixed-Signal processing blocks, Advantages of MAD circuits on the same chip, Applications of MAD chips, Obstacles in the design of MAD chips, Mixed-signal IC design flow, Mixed-signal layout issues, A MAD chip including a built-in self-test structure.

Module-2: Nonlinear Analog Components

12 Hour

Comparators: Comparator specifications, op-amp comparator, charge-injection errors, latched comparators, CMOS comparators, BiCMOS comparators, Bipolar comparators, Sample-and-Hold (S/H) circuits: S/H basics, MOS S/H circuits, CMOS S/H circuits, BiCMOS S/H circuits, BiCMOS S/H circuits, CMOS S/H circuits, BiCMOS S/H circuits, BiCMOS S/H circuits, CMOS S/H circuits, BiCMOS S/H circuits, BiCMO

Module-31: Integrated Analog Filters

12 Hour

Continuous-Time Filters: 1st order and 2nd order filters, Transconductance-C filters, Active RC filters, MOSFET-C filters, Discrete-Time Filters: Basic concepts of discrete-time signals and filters, Switched-Capacitor (SC) circuits - Basic building blocks, basic operation and analysis, 1st order filters, biquad filters, ladder filters, charge injection, SC gain circuits, Amplitude modulator, FWR, peak detector, VCO, sinusoidal oscillator, S/H circuits based on SC circuit

Module-4: Data Converters

12 Hour

Data Converter Fundamentals: Analog vs Discrete-time signals, converting analog signals to digital signals, ideal Digital-to-Analog Converter (DAC), ideal Analog-to-Digital Converter (ADC), Sample-and-Hold (S/H) characteristics, quantization noise, signed codes, DAC specifications, ADC specifications, Mixed-signal layout issues.

DAC Architectures: Decoder-based DACs, Binary-scaled DACs, Thermometer-code DACs, Hybrid DACs, ADC Architectures: Integrating ADC, Successive-Approximation ADC, Cyclic ADC, Pipelined ADC, Flash ADC, Two-step ADC, Interpolating ADC, Folding ADC, Time-interleaved ADC

Module-5: Phase-Locked Loops (PLL)

Basic PLL architecture, Application of PLL as electronic oscillators and frequency synthesizer, Delay-locked loop, PLL with BIST structure

Learning Resources

- 1. Tony Chan Carusone, David A. Johns, Kenneth W. Martin, "Analog Integrated Circuit Design", Wiley, 2012.
- 2. Tertulien Ndjountche, "CMOS Analog Integrated Circuits: High-Speed and Power-Efficient Design", CRC Press, 2011.
- 3. Jacob Baker, "CMOS Mixed-Signal circuit design", IEEE Press, 2009.
- 4. Razavi, "Principles of data conversion system design", Wiley IEEE Press, 1st Edition, 1994.
- 5. Franco Maloberti, "Data Converters", Springer, 2007.

- 6. Vineeta P. Gejji, "Analog and Mixed Model VLSI Design", PHI, 2011.
- 7. Willy M. C. Sansen, "Analog Design Essentials", Springer, 2006.
- 8. Arjuna Marzuki, "CMOS Analog and Mixed-Signal Circuit Design", CRC Press, 2020.
- Gregorian, Temes, "Analog MOS Integrated Circuit for signal processing", John Wiley and Sons, 1986.
- 10. Rolf Schaumann, Haiqiao Xiao, Mac E. Van Valkenburg, "Analog Filter Design", Oxford University Press, Second Edition, Re-print, 2013.

Learning Assessment					12 17			
	Blo <mark>om</mark> 's		2.07.15	Continuous Learning	Assessment (CLA)		Summa	
	Level of Thinking		Forma CLA-1 Average (50%	of unit tests	1 2 No. 1 No	Learning A-2 0%)	Final Exam (40% weig	
			Theory	Practice	Theory	Practice	Theory	Practice
Level 1	Remember		20%	1,7 To 2003 1 10	20%		20%	-
Level 2	Understand		20%		20%		20%	-
Level 3	Apply		30%	14 A	30%	A- H	30%	-
Level 4	Analyze		30%		30%)-	30%	-
Level 5	Evaluate					A - 1	-	-
Level 6	Create	-	100	-11/1/->	-		-	-
	Total	_ P	100	%	100	0 %	100 %	ó

Course Designers		
Experts from Industry	Experts from Higher Technical Institutions	Int <mark>ernal</mark> Experts
1. Mr. Sethupathy Balakrishnan, Lead Application Engineer, Cadence		1. Dr. A.V.M. Manikandan, SRMIST
Designs Systems	Engineering, College of Engineering Guindy, Anna University	
	2. Prof. Binsu J Kailath, Dept of Electronics Engineering, IIITDM,	2. Dr. T. Vijayan, SRMIST
	Kancheepuram	

Course	21FCF632T Course	RADIO EREOLIENCY VI SI	Course	PROFESSIONAL ELECTIVE	L	Т	Р	C	
Code	Name	RADIO FREQUENCY VLSI	Category	PROFESSIONAL ELECTIVE	3	0	0	3	

Pre-requisite Courses	20ECC	533J Co- requisite Courses	Nil R	Progressive Courses	Nil
Course Offeri	ng Department	Electronics and Communication Engineering	Data Book / Codes / Standards	2 A 3	Nil

Course Learning Rationale (CLR):	The purpose of learning this course is to:
CLR-1:	understand the basic architectures of RF systems and its characteristic parameters, Impedance matching techniques.
CLR-2:	construct the different types of filters.
CLR-3:	utilize the basics of High frequency amplifier design, the operation of Mixers, oscillators, PLL and Frequency synthesizers
	identify different types of Power amplifiers
CLR-5:	understand Various multiple access techniques and Construct LNA, Frequency synthesizer and power amplifier

Course Outcomes	At the end of this course, learners will be able to:	Programme Outcomes (PO)				
(CO):	At the end of this course, learners will be able to.		1		2	3
CO-1:	construct impedanc <mark>e match</mark> ing networks		3		3	2
CO-2:	implement the different types of filters.		3		3	2
CO-3:	describe High frequ <mark>ency am</mark> plifier design, the operation of Mixers, oscillators, PLL and Frequency synthesizers		3		3	2
CO-4:	characterize the different types of Power amplifiers		3		3	2
CO-5:	recognize Various multiple access techniques and Create LNA, Frequency synthesizer and power amplifier		3		3	2

Module-1 - RF Systems 9 Hour

Basic architectures, Transmission media and reflections Maximum power transfer, Passive RLC Networks, Parallel RLC tank Circuit, Q factor, Series RLC networks, Problems solving on RLC networks, Interconnects and skin effect, Conditions for Impedance matching, Pi and T matching network, Problems solving on Matching network, Performance parameter of RF design, Gain Parameters, Non-linearity parameters, Noise figure, Phase Noise, Dynamic range, Performance tradeoffs in an RF circuit.

Module-2 - : Filter Design & High Frequency Amplifier Design

9 Hour

Filter performance parameters and its types, Frequency and impedance scaling, Modern filter design, Derivation of normalized parameters, Low Pass, High Pass, Band Pass and Band Reject Filter Design, Microstrip based filter design, Effects of finite Q, High frequency Amplifier design, Shunt-series Amplifier, Bandwidth enhancement techniques, tuned amplifiers, Neutralization, Unilateralization, cascaded Amplifiers, Problems solving on RF amplifier design.

Module-3 – Mixers and Oscillators 9 Hour

Introduction to RF active devices, Mixer fundamentals, Nonlinear systems as Linear mixers, Multiplier based mixers, Subsampling mixers, Oscillators - Problems with purely linear oscillators, Resonators, Tuned oscillator- Hartley, Colpitt, Clapp oscillator, Negative Resistance oscillators, Voltage controlled oscillators, Phase locked loops: Linearized PLL models, Phase detectors, Charge pumps, Loop filters, PLL design, Frequency synthesizer: Block diagram description, Integer-N synthesis, Fractional-N frequency synthesis, Applications of Frequency Synthesis, Problem Solving on Oscillator and PLL.

Module-4 - RF Power Amplifiers 9 Hour

General considerations and its performance metrics, Types of Power amplifiers, Class A, B, AB, C, D, E, F & Efficiency Derivation, Linearization Techniques and methods, Envelope feedback, Feed forward, Pre-Post distortion, Envelope elimination and restoration, Efficiency Boosting Techniques, Methods of Efficiency boosting, Adaptive bias, Doherty amplifier, RF Power amplifier design examples.

Module-5 – Multiple Access Techniques & Case Studies

Introduction, Various multiple access Techniques, Wireless standards, Mobile RF communication, FDMA, TDMA, CDMA, Transceiver Architectures: General considerations, Receiver architecture, Transmitter Architecture, OOK Transceiver, Transceiver performance tests, Transceiver Design examples, CASE STUDIES: LNA Design, Mixer Design, Frequency Synthesizer, Power Amplifier.

Learning Resources
Resources

- 1. Aleksandar Tasic, Wouter.A.Serdijn, John.R.Long, "Adaptive Low Power Circuits for Wireless 5. Communication (Analog Circuits and Signal Processing)", Springer, 2nd Edition, 2010.
- 2. Chris Bowick, "RF Circuit design", Newnes (An imprint of Elsevier Science), 2nd Edition, 2007.
- 3. B.Razavi ,"RF Microelectronics", Prentice-Hall ,2nd Edition, 2020.
- 4. Bosco H Leung "VLSI for Wireless Communication", Pearson Education, 2nd Edition, 2011.
- Behzad Razavi, "Design of Analog CMOS Integrated Circuits" McGraw-Hill, 2nd Edition, 2017.
- Jia-sheng Hong, "Microstrip filters for RF/Microwave applications", Wiley, 2nd Edition, 2011.
- Thomas.H. Lee, "The design of CMOS Radio-Frequency Integrated Circuits", Cambridge University Press, 2nd Edition, 2004.

l	Learr	ing	<u>Asse</u>	ssm	en

	Bloom's Level of Thin <mark>king</mark>	CLA-1 Avera	Continuous Learning native ge of unit test 0%)	g Assessment (CLA) Life-Long CL/ (10	4-2	Summative Final Examination (40% weightage)		
	- A-17	Theory	Practice	Theory	Practice	Theory	Practice	
Level 1	Remember	20%		20%		20%	-	
Level 2	Understand	20%	3.5 P. S.	20%		20%	-	
Level 3	Apply	30%	C 100 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	30%		30%	-	
Level 4	Analyze	30%	Talk of the sear Well	30%	77 . Jan - 18-4	30%	-	
Level 5	Evaluate	3 3777		12 May 12 May 18	- C	-	-	
Level 6	Create	25.00	The Property of the	· 西京美国等国		-	-	
	Total	10	0%	100)%	100%		

Course Designers	
Experts from Industry	Experts from Higher Technical Institutions Internal Experts
1. Mrs. A. Suganya, Sr. Scientist and Head, Hardware Security	1. Prof Meenakshi M, Dept of Electronics and Communication Engineering, 1. Dr. J. Manjula, SRMIST
	2. Prof. Binsu J Kailath, Dept of Electronics Engineering, IIITDM, Vandoopuram
	Kancheepuram



Course	21ECE633T	Course	MACHINE LEARNING IN VLSI	Course	Ε	PROFESSIONAL ELECTIVE	L	T	Р	С
Code		Name		Category			3	0	0	3
					4					

Pre-requisite	I	Vil	Co- requisite		Nil	Progressive Progressive		Nil
Courses			Courses	_+" .		Courses		
Course Offering	ng Department	Electronics ar	nd Communic <mark>ation En</mark> g	ineering	Data Book / Codes /	TO Service Control	Nil	
	•				Standards	18 1		
·				1				

Course Learning Rationale (CLR):	The purpose of learning this course is to:
CLR-1:	provide concise introduction to the fundamental concepts of machine learning
CLR-2:	introduce neural networks and its algorithm
CLR-3:	focus on the backend design challenges, including mask synthesis and physical verification
CLR-4:	study how machine le <mark>arning c</mark> an help in physical design
CLR-5:	address the energy efficient design of machine learning hardware

Course	At the end of this course, learners will be able to:	Programme Outcomes (PO)					
Outcomes (CO):		1	1	2	3		
CO-1:	understand the basic definitions and concepts of machine learning	3		2	-		
CO-2:	explore the applica <mark>tions of n</mark> eural network algorithms	3		2	-		
CO-3:	apply the machine <mark>learning</mark> in physical verification and mask synthesis			2	3		
CO-4:	predict the machin <mark>e learnin</mark> g model for physical design such as placement and routing			2	3		
CO-5:	analyze the energy <mark>efficient</mark> machine learning hardware structures.			2	3		

Module-1 - Introduction to Machine Learning

9 Hour

Introduction, Types of Learning, Supervised learning: Classification and Regression, Unsupervised Learning: Clustering, Density Estimation, Reinforcement learning, Linear Regression, Types of Regression Models, Tutorial on regression, Decision Tree, Example for Decision Tree, Overfitting, Pruning, Principal components, Bayesian Learning, Bayesian Network

Module-2 - Neural Network, Computational Learning Theory and Clustering

9 Hour

Neural Network Introduction, Perceptrons, Multilayer Neural Network, Back Propagation Algorithm, Deep Neural Networks, Training of neural networks, Introduction to computational learning theory, Sample Complexity, Finite hypothesis space, Infinite hypothesis space, Ensemble Learning, Bootstrap Method, Bootstrap Aggregation, Adaptive Boosting (AdaBoost) Algorithms, Gradient Boosting Algorithms, Clustering, Hierarchical, Model Based and Density Based Clustering, K-means Clustering

Module-3 - Machine Learning in Physical Verification and Mask Synthesis

9 Hour

Machine learning taxonomy, VLSI CAD Abstraction levels, Machine Learning for Compact Lithographic Process: Introduction, Lithographic Patterning Process, Representation of Lithographic Patterning Process – Mask, Imaging, Resist & Etch Transfer Function, Machine Learning for Mask Synthesis: Machine Learning guided OPC, MLP Construction, ML-EPC, EPC Algorithm, CPM Task, CPM Training Experience, Performance metrics, Supervised learning of a CPM.

Module-4 - Machine Learning Applications in IC Physical Design

Hour

Machine Learning for Manufacturing: Gaussian Process-Based Regression Models, and Routability-Driven Placement, Lithography Friendly Routing, Gaussian Process-Based Wafer-Level Correlation Modeling, Wafer-Level Statistical Correlations, Spatial Correlation Modeling of E-Test Measurement, Probe-Test Specification Measurements, Machine Learning Approaches for IC Manufacturing, Manufacturing Process, Evaluation Metric: Confusion Matrix, ROC Curves

Module-5 – Energy Efficient Design of Advanced Machine Learning Hardware

9 Hour

Artificial Intelligence and Machine Learning, Neural Networks, Resource Requirements of State-of-the-Art Neural Networks, Software and Co-design Optimizations, Pruning, Weight Sharing, Compact Network Architectures, Hardware–Software Co-design, Hardware–Level Techniques, Deep CNN Accelerators, Memory-Efficient Architectures, Leveraging Sparsity in Neural Networks, Error Resilience Analysis, Efficient Machine Learning Architectures.

Learning Resources	Rosasco, (2017), Introductory Machine Learning Notes. Ipaydin, Introduction to Machine Learning, Second Edition.	FN	3. Ibrahim (Abe) M. Elfadel, Duane S. Boning and Xin Li (2019), Machine Learning in VLSI Computer Aided Design
		111 4	

Learning Assessme	ent	· / ·	1		/// .			
	Bloom's		Continuous Learning	Sun	nmative			
	Level of Thinking		mative	Life-Long	g Learning	Final Examination		
		CLA-1 Average of unit test CLA-2		(40% v	veightage)			
		(5	0%)	(10	0%)			
		Theory	Practice	Theory	Practice	<u>Theory</u>	Practice	
Level 1	Remember	20%	A PLOOP	20%	- ()	20%	-	
Level 2	Understand	20%	自2014年4月18日	20%		20%	-	
Level 3	Apply	30%	14 To 14 To 14 To 15 To	30%		30 %	-	
Level 4	Analyze	30%	A 255 V	30%		30%	-	
Level 5	Evaluate	FA 1-	College of the said	William Co.	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	-0	-	
Level 6	Create	- A	12 St. 1 St. 10	F1 48 1 1 1 1 1 1	JN 175		-	
	Tot <mark>al </mark>	10	00 %	10	0 %	1	00 %	

Course Designers		7 7
Experts from Industry	Experts from Higher Technical Institutions	Internal Experts
1. Mrs. A. Suganya, Sr. Scientist and Head, Hardware		1. Dr. A. Manikanda <mark>n, SRMI</mark> ST
Security Research Group, SETS, Chennai	Engineering, College of Engineering Guindy, Anna University	
policies and the second	2. Prof. Binsu J Kailath, Dept of Electronics Engineering, IIITDM,	
	Kancheepuram	

Course	21FCF63/IT Course	FUNDAMENTALS OF SOLAR CELL	Course	Е	PROFESSIONAL ELECTIVE	L	Т	Р	C	٦
Code	Name	FUNDAMENTALS OF SOLAR CELL	Category		PROFESSIONAL ELECTIVE	3	0	0	3	

Pre-requisite Courses	Ni	Co- requisite Courses	Nil	Progressive Courses	Nil	
Course Offeria	ng Department	Electronics and Communication Engineering	Data Book / Codes / Standards		Nil	

Course Learning Rationale (CLR):	The purpose of learning this course is to:
	know the fundamentals of semi <mark>conductor</mark> materials for solar cells.
CLR-2:	understand the basics of solar cell design and parameters
CLR-3:	introduce the technologies for solar cell production with silicon material
	apply the solar cell technologies foe wafer-based silicon
CLR-5:	implement the silicon tec <mark>hnologie</mark> s for photovoltaic systems

Course Outcomes	At the end of this course, learners will be able to:		Progra	amme Outcomes (PO)
(CO):	At the end of this course, learners will be able to.	1		2	3
CO-1:	define the principles and arrangements of silicon atoms and p-n junction under illumination	3		2	-
CO-2:	acquire knowledge on solar cell parameters for efficient design	3		-	3
CO-3:	analyse the growth process of metallurgical and electronic grade silicon	3		2	-
CO-4:	express the knowle <mark>dge of s</mark> olar cell technology for development of commercial solar cell	3		-	2
CO-5:	investigate the design and application of photovoltaic systems	3		2	-

Module-1 - Fundamentals of Semiconductors

9 Hour

Semiconductor as solar cell materials; arrangement of atoms in space: types of unit cells and lattices in solar cell; P-N junction diode, equilibrium conditions: carrier movement, current densities and carrier concentration profiles; P-N junction in non-equilibrium: I-V relation quantitative analysis; P-N junction under illumination: solar cell: generation of photovoltaics, light generated current, I-V equation of solar cell, solar cell characteristics.

Module-2 - Design of Solar Cell

9 Hour

Upper limits of cell parameters: short circuit current, open circuit voltage, Fill Factor, Efficiency; Losses in solar cell: model of a solar cell, effect of series and shunt resistance on efficiency, effect of solar radiation in efficiency effect of solar radiation in solar cell parameters: short circuit current, open circuit voltage, Fill Factor, Efficiency; Losses in solar cell: model of a solar cell, effect of series and shunt resistance on efficiency, effect of solar radiation in efficiency; solar cell designs; Design of high lsc: requirement of high lsc, choice of junction depth and its orientation, minimization of optical losses, minimization of recombination; Analytical Techniques: solar simulators, I-V measurement, quantum efficiency measurement

Module-3 - Solar Cell Technologies: Production of Si

9 Hour

Growth of solar PV industry and Si requirements; steps in producing Si wafers, production of metallurgical grade Si (MGS), production of electronic grade Si (EGS): high purity Si containing gases, obtaining solid poly-Si; production of Si wafers: monocrystalline Si ingots- CZ and FZ process; refining process for solar grade Si, possible route for conversion of MG-Si to SoG-Si, SI usage in solar PV

Module-4 - Si Wafer-Based Solar Cell Technology

9 Hou

Development of commercial solar cell: improvement from use of CZ single crystal, diffused junction and anti-reflective coating; multi-crystalline Si and first terrestrial PV modules; process flow of commercial Si cell technology; processes used in solar cell technology: saw damage removal and surface texturing, P-N Junction formation – diffusion process, thin film layer for ARC and surface passivation, metal contacts- pattern defining and deposition; High efficiency solar cell: passivated emitter solar cell, buried contact and rear point contact solar cell, passivated emitter and rear contact.

Module-5 - Photovoltaics System Design and Applications

9 Hour

Introduction to solar PV systems; Stand-alone PV system configurations: type-B, type-C and type-D regulated stand-alone system with DC load, Design methodology of PV systems: design of PV-powered DC fan without battery (type-A configuration), regulated stand-alone system with DC load using MPPT (type-B configuration), design of PV powered DC pump, design of stand-alone systems with battery and AC or DC load; hybrid PV systems: Grid connected PV system; Simple payback period.

	1.	Chetan Singh Solanki, Solar Photovoltaic Technology and Systems: A Manual for Technicians, 3.	S. P. Sukhatme, SOLAR ENERGY, 4rth edition, 568 pages, 2017, McGraw hill education.
Learning		Trainers and Engineers, 320 pages, 2013, Prentice Hall India Learning Private Limited. 4.	Hans S. Rauschenbach, Solar Cell Array Design Handbook: The Principles and
Resources	2.	G. N. Tiwari, Arvind Tiwari, Shyam, Handbook of Solar Energy: Theory, Analysis and	Technology of Photovoltaic Energy Conversion, 560 pages, 1980, Springer.
		Applications, 1st edition, 764 pages, 2016, Springer.	

	Continuous Learning Assessment (CLA)					Sumi	Summative	
	Bloom's Level of Thinking	CLA-1 Aver	Formative Life-L CLA-1 Average of unit test (50%)		g Learning LA-2 10%)	Final Examination (40% weightage)		
		Theory	Practice	Theory	Practice	Theory	Practice	
Level 1	Remember	20%		20%		20%	-	
Level 2	Understand	20%	26.0	20%	V 772	20%	-	
Level 3	Apply	30%	100 A 500 S 500	30%	(7-)	30%	-	
Level 4	Analyze	30%	THE PART AND DESCRIPTION OF	30%		30%	-	
Level 5	Evaluate			A. W. 14		-	-	
Level 6	Create		1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	11.	1 7	-	-	
	Total	1	00 %	10	00 %	10	0 %	

Course Designers	· 医克尔克氏试验检 "多名,说是一个"是这种的基础。"	
Experts from Industry	Experts from Higher Technical Institutions	Internal Experts
1. Mr. Abhijeet Pathak, Western Digital, Bangalore, India.	1. Prof. G. P. S. C. Mishra, NIT Raipur	1. Dr Soumyaranja <mark>n Routra</mark> y, SRMIST
	2. Dr. K.P. Pradhan, IIITDM, Kanchipuram	2. Dr Rajesh Agarwal, SRMSIT

Course	21ECE635T	Course	OPTIMIZATION TECHNIQUES IN NANOELECTRONICS	Course	С	PROFESSIONAL ELECTIVE	L	T	Р	С
Code	21000001	Name	OPTIMIZATION TECHNIQUES IN NANOELECTRONICS	Category		PROFESSIONAL ELECTIVE	3	0	0	3

Pre-requisite Courses	N	Co- requisite Courses	Nil	Progressive Courses	Nil	
Course Offeria	ng Department	Electronics and Communication Engineering	Data Book / Codes / Standards		Nil	

Course Learning Rationale (CLR):	The purpose of learning this course is to:
CLR-1:	know the fundamentals of materials for nanoelectronics.
CLR-2:	understand the basics of growth, fabrication, and measurement techniques for nanostructures
CLR-3:	introduce the concepts of electron transport in semiconductors and nanostructures
CLR-4:	apply the electron properties of in traditional low-dimensional structure
CLR-5:	implement the concepts of different nanostructured devices

Course Outcomes	At the end of this course, learners will be able to:	Programme Outcomes (PO)				
(CO):	At the end of this course, learners will be able to.	1		2	3	
CO-1:	know the fundament <mark>als of m</mark> aterials for nanoelectronics.	3		3	-	
CO-2:	understand the basi <mark>cs of gro</mark> wth, fabrication, and measurement techniques for nanostructures	3		3	-	
CO-3:	introduce the conce <mark>pts of el</mark> ectron transport in semiconductors and nanostructures	3		3	-	
CO-4:	apply the electron p <mark>roperties</mark> of in traditional low-dimensional structure	3		-	2	
CO-5:	implement the concepts of different nanostructured devices	3		3	-	

Module-1: Materials for Nanoelectronics 9 Hour

Introduction, Semiconductors, Crystal lattices: bonding in crystals: Ionic crystals, Covalent crystals, Electron energy bands, Symmetry of crystals and properties of electron spectra, Direct-bandgap and indirect-bandgap semiconductors, Band structures of semiconductor alloys, Semiconductor heterostructures, Band offsets at heterojunctions, Graded semiconductors, Strained pseudomorphic heterostructures, Lattice-matched and pseudomorphic heterostructures, Organic semiconductors, Carbon nanomaterials: nanotubes and fullerenes.

Module-2: Optimization of Growth, Fabrication, and Measurement Techniques for Nanostructures

9 Hour

Introduction, Bulk crystal and heterostructure growth: Single-crystal growth, Epitaxial growth, Molecular-beam epitaxy, Nanolithography, etching, and other means for fabrication of nanostructures and nanodevices, Techniques for characterization of nanostructures, Spontaneous formation and ordering of nanostructures, Clusters and nanocrystals, Methods of nanotube growth, Chemical and biological methods for nanoscale fabrication, Fabrication of nano-electromechanical systems

Module 3: Optimization the Electron Transport in Semiconductors and Nanostructures

9 Hour

Introduction, Time and length scales of the electrons in solids: Electron fundamental lengths in solids, Size of a device and electron spectrum quantization, Quantum and classical regimes of electron transport, Statistics of the electrons in solids and nanostructures: Classical statistics, Fermi statistics for electrons, The density of states of electrons in nanostructures, Electron transport in nanostructures: Classical dissipative transport, Dissipative transport in short structures, Hot electrons, Transient overshoot effects, Classical ballistic transport, Quantum ballistic transport: the Landauer formula.

Module-4: Electrons in Traditional Low-Dimensional Structure

9 Hour

Introduction, Electrons in quantum wells: Single modulation-doped heterojunctions, Basic equations describing the physics of the electrons at an interface, Numerical analysis of a single heterojunction, Control of charge transfer, Electrons in quantum wires: Electron transport in quantum wires, Electrons in quantum dots: zero-dimensional system, macro atom, tunnelling of electrons through quantum levels.

Module-5: Device Optimizations and Applications

9 Hour

Geometry and Dimension, Surface Modification, Integration, Resonant-tunneling diodes: The physics underlying the resonant-tunneling effect, Quantitative characteristics of the resonant-tunneling effect, Sequential tunneling, Negative differential resistance under resonant tunneling, A resonant-tunneling diode as a microwave oscillator, Field-effect transistors, Single-electron-transfer devices, Potential-effect transistors. Light-emitting diodes and lasers. solar cells, Computational Models: finite element analysis, density functional theory.

	1.	Vladimir V Mitin, Viatcheslav A. Kochelap, and Michael A. Stroscio. "Introduction to 4.	George W. Hanson, "Fundamentals of Nanoelectronics", Prentice Hall, 20073.Karl Goser,
		nanoelectronics: science, nanotechnology, engineering, and applications", Cambridge University	Peter GlÖsekötter, Jan Dienstuhl, "Nanoelectronics and Nanosystems", Springer, 2004
Loorning		Press, 2008. 5.	Vladimir V. Mitin, Viatcheslav A. Kochelap, Michael A. Stroscio, "Introduction to
Learning Resources	2.	Khurshed Ahmad Shah, Farooq Ahmad Khanday "Nanoscale Electronic Devices and	Nanoelectronics: Science, Nanotechnology, Engineering, and Applications", Cambridge
Resources		Their Applications", CRC Press, 2021.	University Press, 2012
	3.	Rainer Waser (Ed.), "Nanoelectronics and Information Technology", Wiley-VCH, Third, 6.	Sulabha K. Kulkarni "Nanotechnology: Principles and Practices", Third Edition, Springer,
		Completely Revised and Enlarged Edition, 2012.	2015.

	Bloom's Level of Think <mark>ing</mark>	CLA-1 Avera	Continuous Learning A Formative CLA-1 Average of unit test (50%)		Learning A-2 %)	Summative Final Examination (40% weightage)		
	/ 6 /	Theory	Practice	Theory	Practice	Theory	Practice	
Level 1	Remember	20%		20%		20%	-	
Level 2	Understand	20%	A THE WAY DO NOT	20%		20%	-	
Level 3	Apply	30%	the way the same of the same o	30%		30%	-	
Level 4	Analyze	30%	1 1 H - 1 1 1 1 1	30%	. 3 7	30%	-	
Level 5	Evaluate		THE VELLEY PARTY TO A	Section 18 18 18		-	-	
Level 6	Create	- 1 may 1777		1 100 1/20	- 3 - - 3	-	-	
	T <mark>otal </mark>	10	00 %	100	%	100	0 %	
	,	- 14.75		No.				

Course Designers	THE PERSON NAMED IN COLUMN TWO IS NOT THE PERSON NAMED IN COLUMN TWO IS NAMED IN COLUMN TW	\sim \sim
Experts from Industry	Experts from Higher Technical Institutions	Internal Experts
1.Mr. Abhijeet Pathak, Western Digital, Bangalore, India	1. Prof. G. P. S. C. Mishra, NIT Raipur	1. Dr. Arijit Bardhan Roy S <mark>RMIST</mark>
	2. Dr. K.P. Pradhan, IIITDM, Kanchipuram	2. Dr. Rajesh Agarwal, SRMIST

Course	21ECE636T	Course	ELECTRONICS DACKACING ASSEMBLY AND TESTING COURS	Course	_	DDOEESSIONAL ELECTIVE	L	Т	Р	С
Code	21ECE0301	Name	ELECTRONICS PACKAGING, ASSEMBLY AND TESTING	Category	E	PROFESSIONAL ELECTIVE	3	0	0	3

Pre-requisite Courses	Nil	Co- requisite Courses	Nil	Progressive Courses	Nii
Course Offering	Department Electronics and	Communication Engineering	Data Book / Codes / Standards		Nil

Course Learning Rationale (CLR):	The purpose of learning this course is to:
CLR-1:	identify electrical issues encountered and corrective actions taken during packaging
CLR-2:	study of single chip and multi- chip IC packaging
CLR-3:	analyze different types of electronic packaging, materials used and their properties
CLR-4:	identify the challenges faced at different levels of packaging and their solutions.
CLR-5:	design PCB using CAD tools and study of board assembly techniques

Course Outcomes	At the end of this course, learners will be able to:		Pro <mark>gramme</mark> Outcomes (PO)				
(CO):	At the cite of this course, feathers will be able to.	1.7	1	2	3		
CO-1:	understand different electrical issues in packaging		3	3	2		
CO-2:	design of chip le <mark>vel pack</mark> aging	200	3	2	-		
CO-3:	explore different electronic packaging types	4	3	2	-		
CO-4:	analyze the challenges faced in packaging		3	2	3		
CO-5:	design of PCB and understand board assembly techniques		3	-	2		

Module-1- Electrical Issues of Packaging

9 Hour

Signal Distribution, Power distribution, Electromagnetic Interference, Electrical Package design: Capacitance, Resistance and Inductance Interconnect, Transmission Lines, Clock Distribution, Noise Sources, Digital and RF Issues, Processing Technologies, Thin Film deposition, Patterning, Metal to Metal joining.

Module -2 – IC Packaging

9 Hour

Introduction, Packaging Technologies: Single chip packaging: functions, types, materials processes, properties, characteristics, Multi chip packaging: types, design, comparison, Chip and Wire assembly: Die/Wire Assembly, Flip Chip Assembly, Wafer level Packaging, wafer level burn – in and test.

Module 3- Advanced Packaging

9 Hour

Functions of an Electronic Packaging — Packaging Hie<mark>rarchy, IC packaging: MEMS</mark> packaging, consumer electronics packaging, medical electronics packaging, Trends: Challenges, Materials for Microelectronic packaging: Material Properties, Ceramics, Polymers, Metals, Material for high density interconnect substrates.

Module -4 – Packaging Challenges

9 Hour

Basic concepts, Thermal mismatch and fatigue – failures – thermo mechanically induced – electrically induced – chemically induced. Thermal Management: Heat transfer fundamentals, Solution- Device level, Package level, convection- heat sink, Electric field control, Enhanced cooling.

Practice: Developing a package for thermal management using COMSOL

Module -5 - Board Assembly and Testing

9 Hour

PCB design- components, standard fabrication, CAD tools for PCB design, Types of Boards. Board assembly- Surface mount technology, Through Hole technology, Process control and design consideration, Rules for Component in PCB, Rules for Power supply and Ground, Connections layout.

Practice: PCB Layout Design of single digit pulse counter using PCB design tool

Learning	1.	Tummala, Rao R., Fundamentals of Microsystems Packaging, McGraw Hill, 2001	4. Qin et.al. "Thermal management and packaging of wide and ultra-wide bandgap power devices: a
Resources	2.	Howard Johnson, Martin Graham, Hig <mark>h Speed Digital</mark> Design: A Handbook of Black	review and perspective" 2023 J. Phys. D: Appl. Phys. 56 093001. 10.1088/1361-6463/acb4ff.
		Magic, Prentice Hall, 1993	
	3.	John H. lau, Semiconductor Ad <mark>vanced Pack</mark> aging, Springer, 2021.	_ ~ 4/2.
		doi.org/10.1007/978-981-16- <mark>1376-0.</mark>	

Learning Assessmer	nt	AYA	a cibic Vi	22			
	Continuous Learning Assessment (CLA) Formative Bloom's Level of Thinking CLA-1 Average of unit test (50%)				Summative Final Examination (40% weightage)		
		Theory	Practice	Theory	Practice	Theory	Practice
evel 1	Rem <mark>em</mark> ber -	15%	12 May 12	15%		15%	-
evel 2	Und <mark>erstand</mark> =	25%		20%	77 July - Jan	25%	-
evel 3	Apply —	30%	A 1984 Y Y Y	25%		30%	-
evel 4	A <mark>nalyze</mark>	30%	A STATE OF THE STA	25%		30%	-
evel 5	E <mark>valuate</mark>	- E-12		10%		-	-
evel 6	<u>Cre</u> ate	3-9 \(\(\) = 1	The second of the	5%	- L	-	-
	T <mark>otal</mark>	100	%		0 %	10	00 %

Course Designers		1000	<i>j</i> / 9	
Experts from Industry		Experts from Higher Technical Institutions	Internal Exp	perts
1. Dr. Sandeep Patil, CEO, EspinNanotech	Solutions, IIT Kanpur	1. Prof Meenakshi M, Dept of Electronics Engineering, College of Engineering Guin		ka Sri <mark>vastava,</mark> SRMIST
	13/	2. Prof. Binsu J Kailath, Dept of Electronic Kancheepuram	s Engineering, IIITDM, 2. Dr. P. E	Eswaran, SRMIST

Course	21FCF637T Course	OLIANTLIM CRYPTOGRAPHY	Course	Е	PROFESSIONAL ELECTIVE	L	Т	Р	С	
Code	Name	QUANTUM CRTFTOGRAFITI	Category	E	FROFESSIONAL ELECTIVE	3	0	0	3	

Pre-requisite Courses	Ni	Co- requisite Courses		Nil	Progressive Courses		Nil
Course Offer	ing Department	Electronics and Communication Electronics	<mark>ngineeri</mark> ng	Data Book / Codes / Standards		Nil	
_					,**		

Course Learning Rationale (CLR):	The purpose of learning this course is to:
CLR-1:	develop a solid understanding of encryption fundamentals, block ciphers like DES and AES, and key distribution mechanisms.
CLR-2:	master public key cryptosystems including RSA, hash functions, MAC algorithms, and digital signatures for data integrity and authentication.
CLR-3:	delve into quantum key distribution with protocols like BB84 and Ekert91 and understand strategies for countering eavesdropping in quantum communication.
CLR-4:	examine quantum computing's impact on cryptography, explore post-quantum techniques, and discuss their role in quantum-safe communication.
CLR-5:	explore on the mathematical based quantum cryptography.

Course Outcomes	At the end of this course, learners will be able to:	Progra	amme Out (PO)	lcomes
(CO):		1	2	3
CO-1:	gain a comprehensive understanding of encryption basics, block ciphers, and key distribution for secure communication.	3	2	3
CO-2:	master RSA encryption, hashing, MAC algorithms, and digital signatures for data integrity and authentication.	3	2	3
CO-3:	apply quantum ke <mark>y distribu</mark> tion protocols, ensuring privacy and countering eavesdropping in quantum communication.	3	2	3
CO-4:	explore quantum computing's impact on cryptography.	3	2	3
CO-5:	implement techniques for quantum-safe communication and data protection.	3	2	3

Module-1 - Foundations of Cryptography

9 Hour

Introduction to Encryption and Block Ciphers - Overview of encryption fundamentals - Introduction to block ciphers - Data Encryption Standard (DES) and its overview - Advanced Encryption Standard (AES) and its significance - Block cipher modes of operation- Public Key Encryption and Key Exchange - Principles of public key cryptosystems - RSA algorithm and its significance - Diffie-Hellman Key Exchange protocol

Module-2 - Cryptographic Protocols and Security Mechanisms

9 Hour

Hashing and Message Authentication Codes (MAC) - Introduction to hashing algorithms - Message Authentication Codes (MAC) - Digital signatures and their importance- Authentication Protocols and System Security - Overview of authentication protocols - Secure email protocols: PGP and S/MIME - Introduction to IP Security (IPsec) - Web security protocols: SSL/TLS - Intrusion detection and prevention systems

Module-3 - Quantum Key Distribution Protocols

9 Hour

Quantum Key Distribution - Significance of random keys - BB84 protocol: Assumptions, Protocol, Relaxing assumptions - Error correction and privacy amplification - Eavesdropping strategies - Entanglement-based QKD: BBM92 protocol. Ekert91 protocol.

Module-4 – Modern Cryptography

9 Hour

Overview of contemporary cryptographic techniques - Quantum Computing Impact - Discussion on the potential threat of quantum computers — Code based cryptography - The security of computing syndromes as one-way function - Codes and structures

Module-5 – Post Quantum Cryptography

9 Hour

Multivariant – Examples of Multivariate PKCs - Lattice based cryptography - Finding Short Vectors in Random q-ary Lattices - Hash Functions - Public Key Encryption Schemes - Use Cases in Quantum Cryptography – Quantum safe cryptography – Quantum random number generation – Quantum secure direct communication.

	1. William Stallings, Cryptography and Network Security, 6th Edition, Pearson Education, March	3. NIST Post Quantum Cryptography, Available online: https://csrc.nist.gov/projects/post-
Learning	2013.	quantum-cryptography/round-2-submissions
Resources	2. Quantum Cryptography. D. Unruh:, Available online:	4. Quantum Algorithms for Cryptographically Significant Boolean Functions - An IBMQ
	https://courses.cs.ut.ee/all/MTAT.07.024/2017_fall/uploads/	Experience. SAPV Tharrmashastha, D. Bera, A. Maitra and S. Maitra, Springer 2020.

earning Assessme	ent						
	Bloom's Level of Thinking	Form CLA-1 Averaç (50	ative ge of unit test	CL	g Learning A-2 0%)	Final Exa	native amination eightage)
		Theory	Practice	Theory	Practice Practice	Theory	Practice
Level 1	Remember	30%	-	30%	A - V	30%	-
Level 2	Understand	30%	الإساني،	30%		30%	-
Level 3	Apply	20%	9,479,170,171	20%		20%	-
Level 4	Analyze	10%	47 F. Style	10%		10%	-
Level 5	Evaluate	10%		10%	(-7,	10%	-
Level 6	Create			The State of the S			-
	Tot <mark>al</mark>	100	%	100	0 %	100) %

Course Designers		
Experts from Industry	Experts from Higher Technical Institutions	Internal Experts
1. Mrs. A. Suganya, Sr. Scientist and Head, Hardware Security	1. Prof Meenakshi M, Dept of Electronics and Communication	1 Dr. D. Drithiviroi CDMIST
	Prof. Binsu J Kallath, Dept of Electronics Engineering, IIITDM, Kanahananananananananananananananananana	2 Dr. Cavathri, SPMIST
	Kancheepuram	Z. Dr. Gayatriri, Skiviis i

Course	21FCF638T Course	RELIABILITY ENGINEERING OF IC TECHNOLOGY	Course _	PROFESSIONAL ELECTIVE	L	Τ	Р	С	
Code	Name	RELIABILITY ENGINEERING OF IC TECHNOLOGY	Category	PROFESSIONAL ELECTIVE	3	0	0	3	

Pre-requisite Courses	N	Co- requisite Courses	Nil	Progressive Courses	Nil	
Course Offeri	ng Department	Electronics and Communication Engineering	Data Book / Codes / Standards		Nil	

Course Learning Rationale (CLR):	The purpose of learning this course is to:
CLR-1:	understand the concept of Reliability technology of IC
CLR-2:	illustrate the degradation mech <mark>anism in S</mark> emiconductor Devices
CLR-3:	apply the mathematics of failure analysis models
CLR-4:	analyze the components reliability
CLR-5:	improve reliability by apply <mark>ing diffe</mark> rent techniques.

Course Outcomes	At the end of this course, learners will be able to:			Program	me Outcomes	(PO)
(CO):	At the end of this course, learners will be able to.			1	2	3
CO-1:	understand the theor <mark>y of Reli</mark> ability Engineering for IC			3	3	-
	discuss the Reliability issues of Electronics Devices	4		3	-	3
CO-3:	design the Mathematical model for Failure Analysis		-	3	3	-
CO-4:	apply life testing for reliability test.			3	-	2
CO-5:	design the techniques for characterization and improvement of reliability of IC			3	3	-

Module-1 - Introduction to Reliability Engineering

9 Hour

Reliability Engineering, Probabilistic Reliability, Repairable and Non-Repairable Items, Pattern of Failures, Evolution of IC technology, current IC device and packaging, Front-End IC Fabrication Operations, Evolution of IC reliability issues and their associated solutions, Failure Physics, Semiconductor Device Degradation and Failure, Bathtub Curve

Module-2 - Reliability of Electronics Devices

9 Hour

Physics of failure – based models for: Mass transport-induced failures, MOSFET Instabilities and Malfunction, Reliability Problems in Memories, Electronic charge-induced failures (Dielectric breakdown, Hot carrier effects, Electrical over-stress and Electrostatic discharge), Environmental damage (moisture ingress, corrosion, radiation damage), Degradation of interconnects (solder creep and fatigue), defects in semiconductor, Processing defects, Yield: Definition and Scope

Module-3 - Introduction to Quality Engineering

9 Hour

Introduction, definition of quality, basic concept of quality, statistics, definition of SQC, benefits and limitation of statistically quality control (SQC), Quality assurance, Quality cost-Variation in process-factors – process capability – process capability studies and simple problems – Theory of control chart- uses of control chart – Control chart for variables X̄ chart, R chart and σ(S) chart

Module-4 - IC Reliability Methodology

9 Hour

Component Reliability, Physical Significance of Physical Distribution functions, Lot by lot sampling – types – probability of acceptance in single, double, multiple sampling techniques – O.C. (Operating Characteristics) curves – producer's Risk and consumer's Risk. AQL (acceptable quality level), LTPD (lot tolerance percent defective), AQL (Average out going quality limit) concepts-standard sampling plans for AQL (acceptable quality level) and LTPD- uses of standard sampling plans

Module-5 - Failure Mechanisms and Failure Analysis of IC

9 Hour

Dominant failure mechanisms in IC today, Failure analysis of IC, Burn In as reliability Test: Infant mortality, Burn in Procedure, Static and Dynamic Burn In, accelerated life testing (ALT) and highly accelerated life testing (HALT), Technology scaling and Burn In, Non-destructive methods: Optical, X-ray, Acoustic microscope, Electrical characterization, thermal microscope, electron microscope, Raman microscope, FTIR, Destructive methods: decapsulation, SEM and EDX, SIMS, Raman and FTIR, XPS, FIB

	1.	Montgomery, Douglas C. "Introduction to Statistical Quality Control", Hoboken, NJ: Wiley,7th 3.	Patrick D. T. O'connor, and Andre Kleyner. Practical reliability engineering, 5th Edition,
Learning		edition, 2013	John Wiley & Sons, 2012.
Resources	2.	Milton Ohring and Lucian Kasprzak. Reliability and failure of electronic materials and devices. 2 nd 4.	Monohar Mahajan, "Statistical Quality Control", Dhanpat Rai & Sons, 2001.
		Edition, Academic Press, 2014.	

	Bloom's Level of Thinking	Form CLA-1 Avera		Life-Lo	ng Learning CLA-2 (10%)	Final Ex	mative amination eightage)
		Theory	Practice	Theory	Practice	Theory	Practice
Level 1	Remember	20%	140 - 140	20%		20%	-
Level 2	Understand	20%		20%		20%	-
Level 3	Apply	30%	- 1	30%	V 424	30%	-
Level 4	Analyze	30%	100 April 100	30%		30%	-
Level 5	Evaluate						-
Level 6	Create	7		J. 4774 X	1, 12	-	-
	Tot <mark>al</mark>	100)%		100 %	10	0 %

Course Designers	
Experts from Industry	Experts from Higher Technical Institutions Internal Experts
1. Dr. Sandeep Patil EspinNanotech Solu <mark>tions, II</mark> T Kanpur	1. Dr. Cher Ming Tan, Chang Gung University, Taiwan 1. Dr Soumyaranjan Routray, SRMIST,
	2. Dr Rajesh Agarwal, SRMSIT

Course	21NTE510J	Course	SEMICONDUCTOR MANUFACTURING TECHNIQUES	Course	Е	PROFESSIONAL ELECTIVE	L	Т	Р	С
Code		Name		Category			2	0	2	3

Pre-requisite		Nil	Co- requisite	Nil	Progressive	Nil
Courses			Courses		Courses	
		Physics	and Nan <mark>otechnology</mark>	Data Book / Codes / Standar	ds	Nil

Course Learning	The purpose of learning this course is to:
Rationale (CLR):	
CLR-1:	understand the basics unit processes
CLR-2:	grasp the differences <mark>/limitation</mark> s of different process techniques
CLR-3:	study the process mechanisms involved
CLR-4:	study the proces <mark>s Integrat</mark> ion techniques and requires processes involved in final IC
CLR-5:	understand the importance of printed electronics

Course	At the end of this course, learners will be able to:	Progra	mme Ou	tcomes
Outcomes (CO):			(PO)	
		1	2	3
CO-1:	understand the selection of silicon wafers and growth techniques	3	3	2
CO-2:	apply suitable patterning for different device structures	3	3	3
CO-3:	apply the dep <mark>osition a</mark> nd implantation techniques for device making	3	3	2
CO-4:	understand the process integration of a CMOS Technology	3	3	3
CO-5	apply printed process for device applications	2	3	2

Module-1 - Production of Silicon, Epitaxy and Oxidation

12 Hour

Classification of grades of silicon, Production of electronic grade silicon, Czochralski growth technique, float zone growth technique, Silicon wafer shaping, Wafer manufacturing steps and inspection, Overview of types of epitaxy, Definition-epitaxy, Comparison of vapour phase epitaxy (VPE), liquid phase epitaxy (LPE) and molecular beam epitaxy (MBE), Working of MBE process, General epitaxy growth mechanism, Epitaxy growth kinetics and examples, Understanding silicon oxide properties, Thermal oxidation, Silicon oxide growth kinetics, Thin oxide growth

Practice: Wafer cleaning processes, Silicon Oxidation Process

Module-2 - Lithography and Etching Tools

12 Hour

Need and basics of lithography, Optical lithography, Optical lithography controls and mask making, Working concept and controls of e-beam lithography, Resolution of electron beam lithography, X-ray lithography, , Stamp based lithography, Nanoimprint lithography and applications, Etching of silicon, Types- wet and dry etching, Ways of plasma generation for etching processes, Sputter etching, Capacitively coupled plasma, Inductively coupled plasma, Classification of plasma using its density, High density plasma, Reactive ion etching, Deep reactive ion etching and bosh process

Practice: Patterning by photolithography process, Wet chemical etching of silicon dioxide and metal films

Module-3 - Deposition Techniques and Ion Implantation Process

12 Hour

Classification of material deposition techniques, Overview of physical and chemical deposition technique, Resistive heating evaporation, Electron beam heating evaporation, Pulsed laser evaporation, Basics of sputtering, DC and magnetron sources for sputtering, Introduction to atomic layer deposition, Working principle of atomic layer deposition, Concepts of diffusion, Using Fick's diffusion in semiconductor doping, Process of ion implantation, Ion implantation tool, Fundamentals of ion energy loss and stopping, Damage due to implantation, Ion distribution, junction control Carrier recovery using annealing process,

Practice: Deposition AI thin film on the oxidized silicon surface by thermal evaporation and e-beam evaporation, Ion beam implantation process and defect analysis using SRIM software

Module-4 - Isolation, Planarization and Process Integration

12 Hour

Requirements of device isolation, Types of isolation, Local Oxidation of Silicon (LOCOS) and shallow trench isolation (STI) processes for local isolation, Concept of self-alignment, MOS fabrication with self-alignment, Requirement of planarization, Local and global planarization using chemical-mechanical polishing, Concept of well formation with p and n doping, Fabrication process of CMOS inverter-Process Integration, Packaging of Integrated Circuits

Practice: Local anodic oxidation pattern by scanning probe microscopy, MOS capacitor (Study of CV, I-V characteristics)

Module-5 - Printed Electronics Technology

12 Hour

Overview of printing processes,, Advantages of printing, Requirements of printing, Printing tools, Types of fluids for ink, Properties of fluids in printing processes,, Working principle of flexographic printing (FP), Advantages and disadvantages of FP, Working principle of gravure printing (GP), Advantages and disadvantages of GP, Working principle of screen printing (SP), Advantages and disadvantages of SP, Working principle of inkjet printing (IP), Advantages and disadvantages of printed devices Comparison of printed devices with lithographically fabricated devices Concept of hybrid printed electronics, Future of printed low-cost electronics,

Practice: Screen printing process and analysis (Optical and Electrical)

Learning Resources

- Hans H. Gatzen, Volker Saile, Jürg Leuthold, "Micro and Nano Fabrication", Springer 2015
- S. M. Sze, and S. Lee, "Semiconductor Devices Physics and Technology", Wiley, 2012
- 3. Giovanni Nisato, Donald Lupo, Simone Ganz, "Organic and Printed Electronics", CRC Press. 2016.
- 4. Sorab K. Gandhi, "VLSI Fabrication and Principles", McGraw Hill, 2005
- 5. Ulrich Hilleringmann, "Silicon Semiconductor Technology" © Springer Fachmedien Wiesbaden GmbH, 2023

Learning Assessme	ent		Start Land Ville	Secretary Secretary	With the second			
	Bloom's	12/1/20	Continuous Learning	g Assessment (CLA)		Summative		
	Leve <mark>l of Thin</mark> king	Forr	Formative		g Learning	Final Examination		
		CLA-1 Avera	age of unit test	CLA-2	Practice	(40% w	eightage)	
		(4	5%)	(1	5%)			
		Theory	Practice	Theory	Practice	T <mark>he</mark> ory	Practice	
Level 1	Remember	15%	Carl − Naga		15%	15%	-	
Level 2	Understand	25%	- 1		25%	25%	-	
Level 3	Apply	30%	- 11/10/1		30%	30%	=	
Level 4	Analyze	30%	- V(5/4)		30%	30%	-	
Level 5	Evaluate	7.			_ / - /	-	-	
Level 6	Create	7 - 5	ADA: Tr	-	7.0	-	-	
	Total	/ 10	0 %	A P . 1 10	00 %	10	0 %	

Course Designers		
Experts from Industry	Experts from Higher Technical Institutions	Internal Experts
Dr. Saravanan Somasundaram, EMMVEE Group, Bangalore mailto: shrisharavanan@yahoo.co.uk	1. Prof. S. Balakumar, University of Madras, balakumar@unom.ac.in	1. Dr. A. Karthigeyan, SRMIST
Dr. Shanmugasundaram Sakthivel, ARCI, Hyderabad, mailto:ssakthivel@arci.res.in	2. Prof. V Subramanian, IIT Madras, manianvs@iitm.ac.in	2. Dr. Elangovan Elamurugu, SRMIST

Course	21NTE511J	Course	CHARACTERIZATION OF SEMICONDUCTOR MATERIALS	Course	Е	PROFESSIONAL ELECTIVE	L	Τ	Р	С
Code		Name	AND DEVICES				2	0	2	3

Pre-requisite	Nil	Co- requisite	Nil	Progressive	Nil
Courses		Courses		Courses	
Course Offering	Department	Physics and Nanotech <mark>nology</mark>	Data Book / Codes / Standards		Nil
			- 177		

Course Learning	The purpose of learning this course is to:
Rationale (CLR):	
CLR-1:	understand the basics of semiconductor characterization techniques
CLR-2:	analyze the given sample data of different materials characterization
CLR-3:	study the surface and microstructural properties
CLR-4:	study the device characterization
CLR-5:	understand the various techniques involved in semiconductor technology

Course Outcomes (CO):	At the end of this course, learners will be able to:				
		1	2	3	
CO-1:	apply knowledge of characterization techniques using E-beam an X-ray	3	3	2	
CO-2:	perform morphological Characterization of different surfaces	3	3	3	
CO-3:	apply the knowledge of suitable optical and electrical characterization techniques	3	3	2	
CO-4:	analyze device characteristics and perform case studies	3	3	2	

Module-1 - Electron Beam and X-ray Characterization Techniques

15 Hour

Secondary Ion Mass Spectrometry (SIMS), Auger Electron Spectroscopy (AES), Low-Energy Electron Diffraction (LEED), X-Ray Diffraction (XRD), Energy-Dispersive X-Ray Spectroscopy (EDS), X-Ray Photoelectron Spectroscopy (XPS), X-Ray Fluorescence (XRF)

Practice: (Demonstrations and Data analysis) Analyze and Identifying different phases present in the samples from given XRD data. (XPS): Identifying various elements present in a given sample and concentration using a given XPS data

Module-2 - Morphology Characterization Techniques

15 Hour

Atomic Force Microscopy (AFM), Scanning Tunnelling Microscopy (STM). Scanning Electron Microscopy (SEM), Transmission Electron Microscopy (TEM), Electron Beam Induced Current (EBIC) Microscopy

Practice: (Demonstration of SEM, TEM AFM/STM): Estimating the grain size/nanorod size for given SEM/TEM images using Image-J software. AFM: roughness determination, STM: Tunneling and surface morphology

Module-3 - Optical and Electrical Characterization Techniques

15 Hour

Ellipsometry, UV-Visible spectroscopy Fourier Transform Infrared Spectroscopy (FTIR), Photoluminescence (PL), Temperature-dependent Photoluminescence (PL), Raman Spectroscopy, Resistivity, Sheet Resistance and the Four Point Probe method, Hall Effect: Resistivity Measurements and majority carrier concentration, Deep Level Transient Spectroscopy (DLTS), C-V characterization: carrier concentration and interface state density measurements

Practice: Demonstration of PL and Raman spectroscopy Bandgap, Fermi Energy and Defects energy level extraction Hall Effect: carrier concentration, mobility measurement

Module-4 - Device Characterizations Case Studies

15 Hour

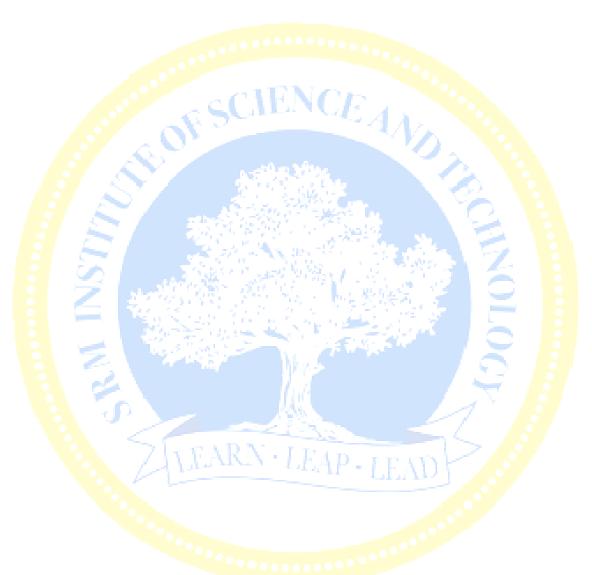
Device Characterizations case studies: MOSFET Characterizations: Threshold voltage, Sub threshold Swing, Interface states. Solar cell Characterizations: Spectral response, Fill factor, Efficiency. Photodetector characterizations: Responsivity, Spectral Response

Practice: Estimation of threshold voltage (VT), Sub-threshold swing (SS) and effective mobility of a MOSFET from CV data, Photodetector performance (Spectral response, Responsivity) extraction using experimentally available data. (Solar Cell): Fill factor and Efficiency of a Solar cell.

Learning	1.	Dieter K. Schroder, "Semiconductor Material and Device Characterization" John	5.	Yang Leng, "Materials Characterization: Introduction to Microscopic and Spectroscopic				
Resources		Wiley & Sons, INC, 3rd Edition.2006		Methods" Wiley online library, 2013.				
	2.	Surender Kumar Sharma, "Handbook of Materials Characterization" Springer		Manijeh Razeghi, Fundamentals of Solid-State Engineering, Springer Cham, 2019				
		International Publishing, 2018	7.	Sateesh Kumar, "Advanced Materials Characterization Basic Principles, Novel				
	3.	Khalid Sultan, "Practical Guide to Materials Characterization: Techniques and		Applications, and Future Directions" Routledge, Taylor & Francis, 2023				
		Applications" Wiley online library, 2022	10	The state of the s				
	4.	S. M. Sze"VLSI technology" McGraw Hill Education, Second edition. 2017						

Learning Assessment									
	Bloom's	Continuous Learning Assessment (CLA)				Summative			
	Level of Thinking	Formative CLA-1 Average of unit test (45%)		Life Long Learning CLA-2 (15%)		Final Examination (40% weightage)			
		Theory	Practice	Theory	Practice	<u>Theory</u>	Practice		
Level 1	Remember	15%	Land Marian		15%	15%	-		
Level 2	Understand	25%	1.00		25%	25%	-		
Level 3	Apply	30%	Read of Park And	to 1 . W	30%	30%	-		
Level 4	Analyze	30%		1 XV 1/2 N	30%	30%	-		
Level 5	Evaluate	- 100		17.9.2 VE (1)		-	-		
Level 6	Create	237 X S	Professional Control	and the state of t		ō -	-		
	<u>Total</u>	-10	00 %	10	0 %	10	0 %		

Course Designers		
Experts from Industry	Experts from Higher Technical Institutions	Internal Experts
Dr. Saravanan Somasundaram, EMMVEE Group, Bangalore mailto: shrisharavanan@yahoo.co.uk	1. Prof. S. Balakumar, University of Madras, balakumar@unom.ac.in	1. Dr. A. Karthi <mark>geyan, SR</mark> MIST
Dr. Shanmugasundaram Sakthivel, ARCI, Hyderabad, mailto:ssakthivel@arci.res.in	2. Prof. V Subramanian, IIT Madras, manianvs@iitm.ac.in	2. Dr. Elang <mark>ovan Ela</mark> murugu, SRMIST



SRM INSTITUTE OF SCIENCE AND TECHNOLOGY

(Deemed to be University u/s 3 of UGC Act, 1956)

Kattankulathur, Chengalpattu District 603203, Tamil Nadu, India